

System Reset IC

■FEATURES

- Full compatible with NJM2103
- Detection Voltage $V_{SA}=4.2V\pm1.0\%$
- Adjustable Detection Voltage $V_{SB}=1.22V\pm1.0\%$
- V_{SA} and V_{SB} have Hysteresis Characteristics at Reset release
- Possible to detect Over Voltage $V_{SC}=1.235V\pm1.0\%$
- Operating Temperature $T_a=-40$ to 125°C
- Low Quiescent Current $280\mu\text{A typ.}$
- Reference Voltage can be taken out $0.8V \text{ typ.}$
- Low reset operation voltage DMP8, DIP8, TVSP8

■GENERAL DESCRIPTION

The NJU2103A is a power supply voltage monitoring IC that instantaneously detects abnormality such as power supply voltage cutoff or drop and generates reset signal.

It can monitor 2 systems of 5 V power supply and arbitrarily set voltage.

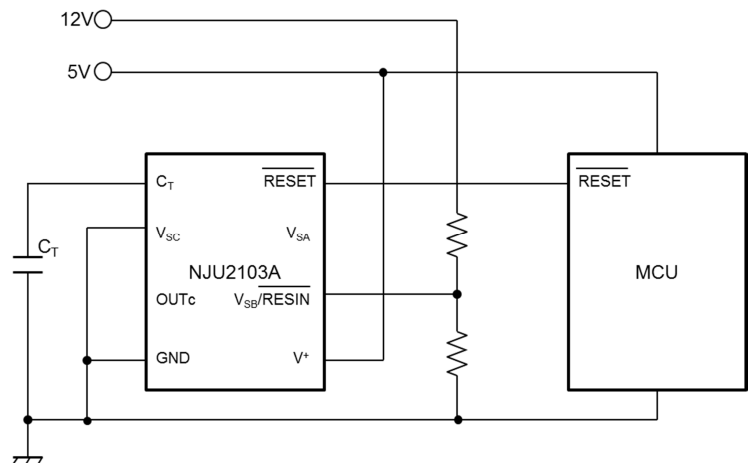
It is possible to direct replacement from NJM2103 and the small TVSP8 package is added.

Furthermore, it improves usability by extending operating temperature, standardizing AC characteristics, and making each parameter highly accurate.

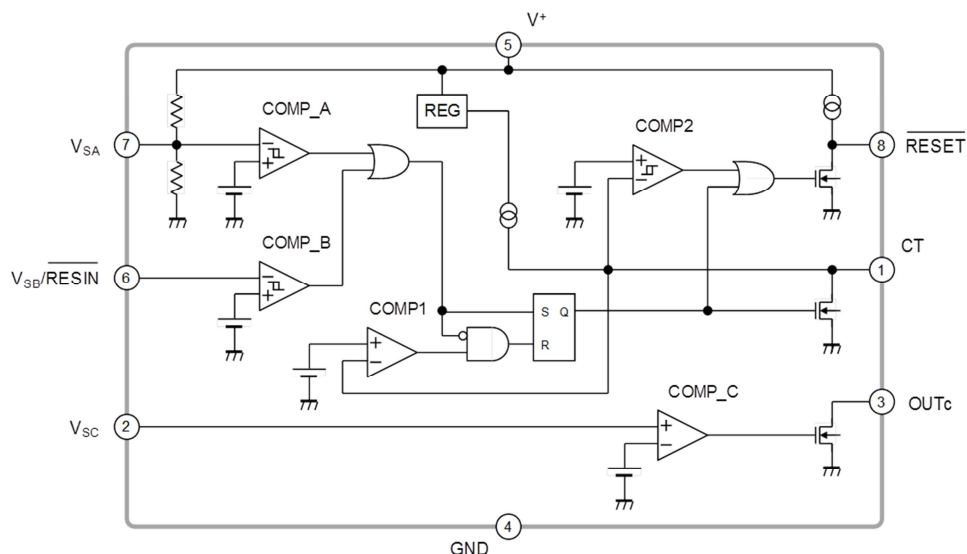
■APPLICATION

- Industrial equipment
- Housing and facility equipment
- OA equipment
- Amusement equipment

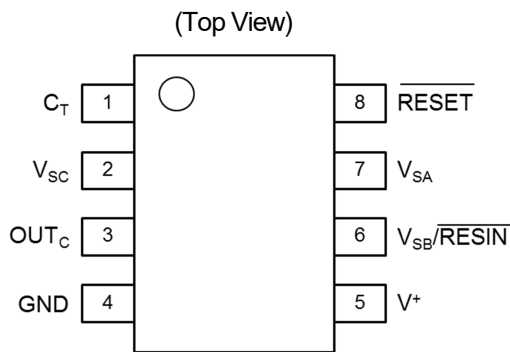
■TYPICAL APPLICATION



■BLOCK DIAGRAM



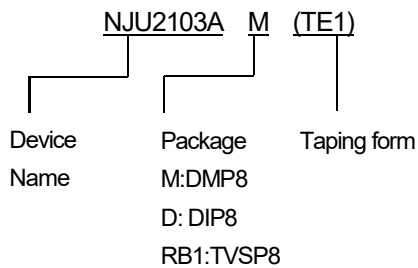
■PIN CONFIGURATION



DMP8/DIP8/TVSP8

PIN No.	PIN NAME	FUNCTION
1	C_T	Connects Capacitor pin for setting RESET Output Pulse Width
2	V_{SC}	Comparator C input pin
3	OUT_C	Comparator C output pin
4	GND	GND pin
5	V^+	Power Supply pin
6	$V_{SB}/RESIN$	Comparator B input pin
7	V_{SA}	Comparator A input pin
8	$\overline{RESET}$	RESET output pin (Active Low)

■PRODUCT NAME INFORMATION



■ORDERING INFORMATION

PRODUCT NAME	PACKAGE OUTLINE	RoHS	Halogen-Free	TERMINAL FINISH	MARKING	WEIGHT (mg)	MOQ (pcs)
NJU2103AM(TE1)	DMP8	○	○	Sn-2Bi	2103A	95	2000
NJU2103AD	DIP8	○	-	Sn-2Bi	2103AD	510	2000
NJU2103ARB1(TE1)	TVSP8	○	○	Sn-2Bi	2103A	18	2000

■ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Supply Voltage	V^+	-0.3 to 20	V
Input Voltage	V_{SA}	-0.3 to $V^+ + 0.3$ (<20)	V
	V_{SB}	-0.3 to 20	V
	V_{SC}	-0.3 to 20	V
C_T Pin Voltage	V_{CT}	-0.3 to $V^+ + 0.3$ (<20)	V
RESET Output Voltage	V_{RESET}	-0.3 to $V^+ + 0.3$ (<20)	V
OUT _C Output Voltage	V_{OUTC}	-0.3 to 20	V
Power Dissipation(Ta=25°C)	P_D	(2-layer / 4-layer)	mW
DMP8		470 ⁽¹⁾ / 600 ⁽²⁾	
DIP8		910 ⁽¹⁾ / 1300 ⁽²⁾	
TVSP8		510 ⁽¹⁾ / 680 ⁽²⁾	
Junction Temperature	T_J	-40 to +150	°C
Operating Temperature	T_{opr}	-40 to +125	°C
Storage Temperature	T_{stg}	-50 to +150	°C

(1): Mounted on glass epoxy board.(76.2 x 114.3 x 1.6 :based on EIA/JEDEC standard, 2 Layers)

(2): Mounted on glass epoxy board.(76.2 x 114.3 x 1.6 :based on EIA/JEDEC standard, 4 Layers) internal Cu area: 74.2 x 74.2mm

■RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	RATINGS	UNIT
Supply Voltage	V^+	2.5 to 18	V
Input Voltage	V_{SA}	0 to V^+	V
	V_{SB}	0 to 18	V
	V_{SC}	0 to 18	V
Output Current	I_{RESET}	0 to 20	mA
	I_{OUTC}	0 to 6	mA
RESET Output Pulse Width	t_{PO}	0.15 to 1500	ms
C_T Capacitor	C_T	0.001 to 10	μF

■ELECTRICAL CHARACTERISTICS

(DC Characteristics)

Unless other noted, $V^+=5V$, $V_{SB}=0V$, $V_{SC}=0V$, $C_T=0.01\mu F$, $T_a=25^\circ C$

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Operating Current 1	I_{CC1}	$V_{SB}=5V$	-	280	390	μA
Operating Current 2	I_{CC2}		-	300	410	μA
V_{SA} Detecting Voltage 1	V_{SAL}	V^+ sweep down, $V_{SB}=V^+$	4.158	4.200	4.242	V
		V^+ sweep down, $V_{SB}=V^+$, $T_a=-40^\circ C$ to $125^\circ C$	4.050	-	4.350	
V_{SA} Detecting Voltage 2	V_{SAH}	V^+ sweep up, $V_{SB}=V^+$	4.210	4.300	4.390	V
		V^+ sweep up, $V_{SB}=V^+$, $T_a=-40^\circ C$ to $125^\circ C$	4.150	-	4.450	
V_{SA} Hysteresis Width	V_{HRSA}		50	100	150	mV
V_{SB} Detecting Voltage	V_{SBL}	V_{SB} sweep down	1.208	1.220	1.232	V
		V_{SB} sweep down, $T_a=-40^\circ C$ to $125^\circ C$	1.190	-	1.250	
V_{SB} Detecting Supply Voltage Fluctuation	ΔV_{SBL}	$V^+=2.5$ to $18V$	-	3	10	mV
V_{SB} Hysteresis Width	V_{HRSB}		14	28	42	mV
V_{SB} Input Current 1	I_{IHB}	$V_{SB}=5V$	-	0	250	nA
V_{SB} Input Current 2	I_{ILB}		-	0	250	nA
High Level RESET Output Voltage	V_{OHR}	$I_{RESET}=-5\mu A$, $V_{SB}=5V$	4.5	4.9	-	V
RESET Output Saturation Voltage 1	V_{OLR1}	$I_{RESET}=3mA$	-	0.05	0.40	V
RESET Output Saturation Voltage 2	V_{OLR2}	$I_{RESET}=10mA$	-	0.15	0.50	V
RESET Output Sink Current	I_{RESET}	$V_{OLR}=1V$	20	60	-	mA
C_T Charge Current	I_{CT}	$V_{SB}=5V$, $V_{CT}=0.5V$	6	9	13	μA
V_{SC} Input Current1	I_{IHC}	$V_{SC}=5V$	-	0	500	nA
V_{SC} Input Current 2	I_{ILC}		-	0	500	nA
V_{SC} Detecting Voltage	V_{SC}		1.223	1.235	1.247	V
		$T_a=-40^\circ C$ to $125^\circ C$	1.195	-	1.275	
V_{SC} Detecting Supply Voltage Fluctuation	ΔV_{SC}	$V^+=2.5$ to $18V$	-	3	10	mV
OUT_C Output Leak Current	I_{OHC}	$V_{OHC}=18V$	-	0	1	μA
OUT_C Output Saturation Voltage	V_{OLC}	$I_{OUTC}=4mA$, $V_{SC}=5V$	-	0.15	0.40	V
OUT_C Output Sink Current	I_{OUTC}	$V_{OLC}=1V$, $V_{SC}=5V$	6	20	-	mA
RESET Minimum Operating Voltage	V_L^+	$V_{OLR}=0.4V$, $I_{RESET}=200\mu A$	-	0.8	1.2	V

■ELECTRICAL CHARACTERISTICS

(AC Characteristics)

Unless other noted, $V^+=5V$, $V_{SB}=5V$, $V_{SC}=0V$, $C_T=0.01\mu F$, $T_a=25^\circ C$

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V_{SA} Input Pulse Width	t_{PIA}		5	-	-	μs
V_{SB} Input Pulse Width	t_{PIB}		5	-	-	μs
RESET Output Pulse Width	t_{PO}	$V_{SB}=V^+$	1.0	1.5	2.0	ms
RESET Rise Time	t_r	$V_{SB}=V^+$, $R_L=2.2k\Omega$, $C_L=100pF$ RESET=10% to 90%	-	1.0	1.5	μs
RESET Fall Time	t_f	$V_{SB}=V^+$, $R_L=2.2k\Omega$, $C_L=100pF$ RESET=90% to 10%	-	0.1	0.5	μs
Output Delay Time	t_{PD}	V_{SB} sweep down	-	2	10	μs
	t_{PHL}	V_{SC} sweep up, $R_L=2.2k\Omega$, $C_L=100pF$	-	0.5	-	μs
	t_{PLH}	V_{SC} sweep down, $R_L=2.2k\Omega$, $C_L=100pF$	-	1.0	-	μs

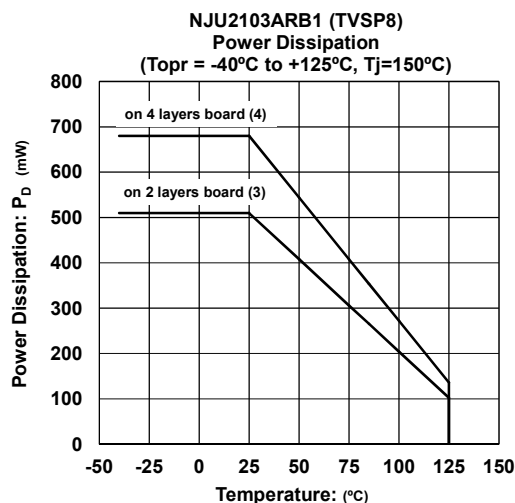
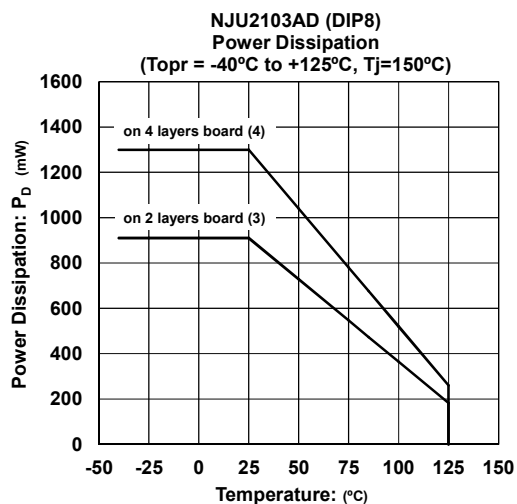
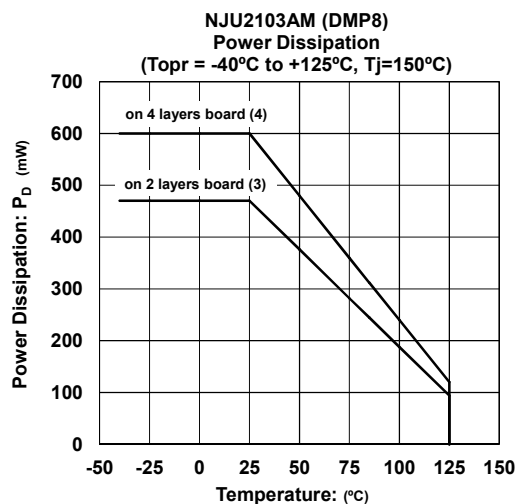
■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE		UNIT
Junction-to-ambient thermal resistance	θ_{ja}	DMP8	262 ⁽³⁾ 206 ⁽⁴⁾	°C/W
		DIP8	138 ⁽³⁾ 98 ⁽⁴⁾	
		TVSP8	244 ⁽³⁾ 185 ⁽⁴⁾	
Junction-to-Top of package characterization parameter	ψ_{jt}	DMP8	72 ⁽³⁾ 65 ⁽⁴⁾	°C/W
		DIP8	57 ⁽³⁾ 54 ⁽⁴⁾	
		TVSP8	51 ⁽³⁾ 45 ⁽⁴⁾	

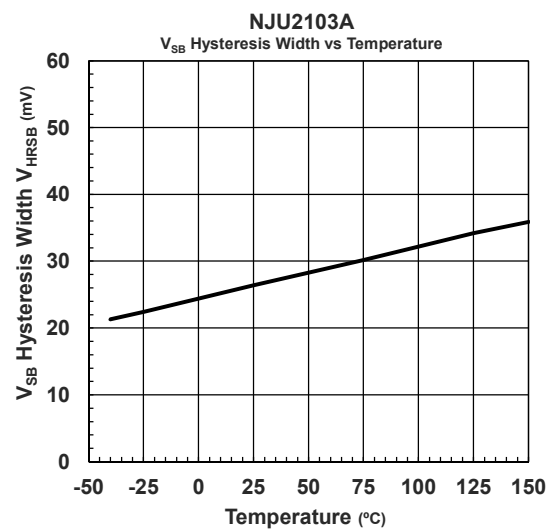
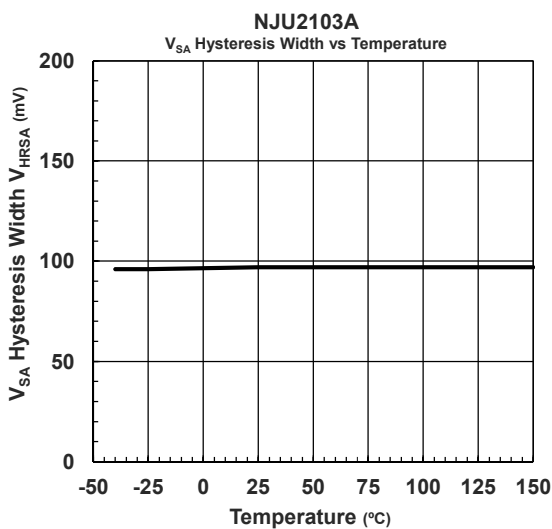
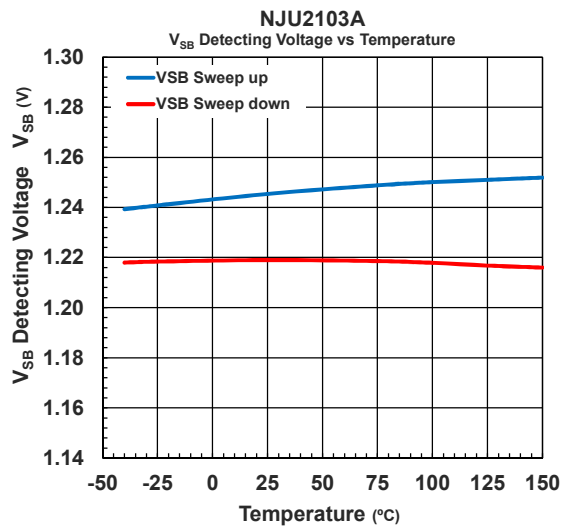
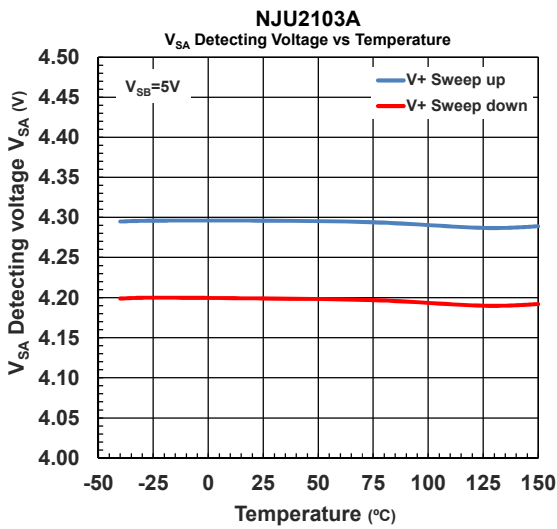
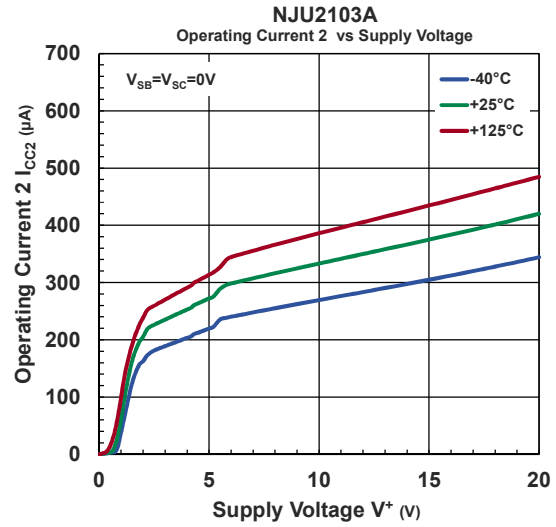
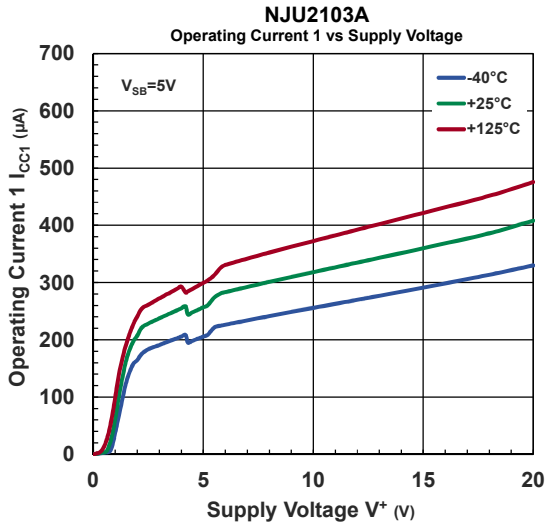
(3): Mounted on glass epoxy board.(76.2 x 114.3 x 1.6 :based on EIA/JEDEC standard, 2 Layers)

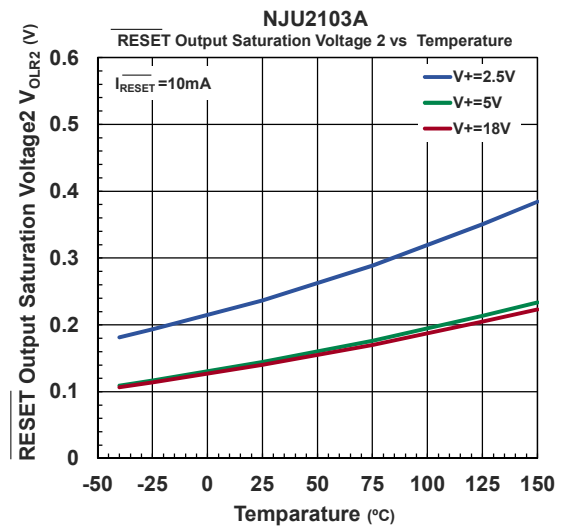
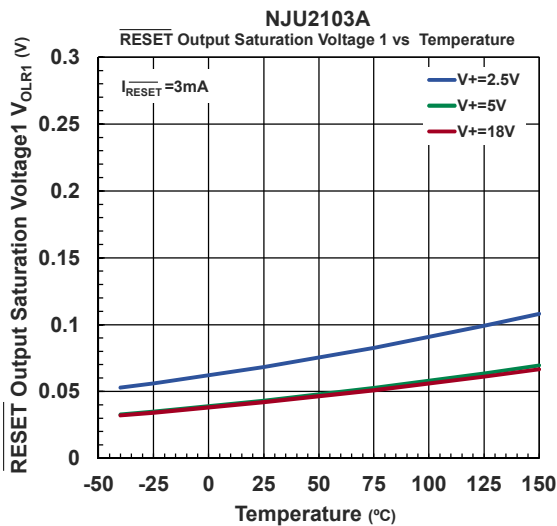
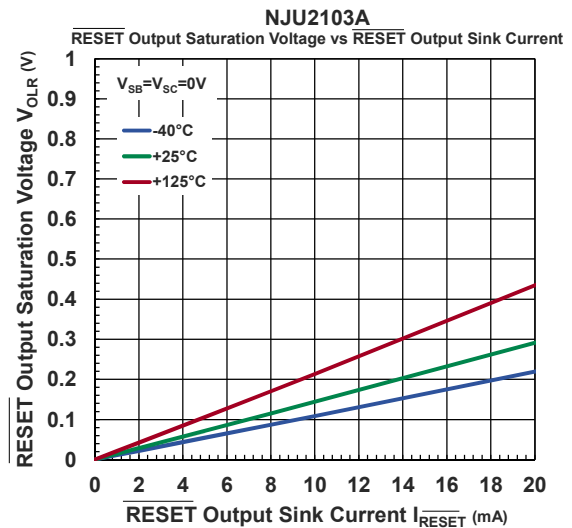
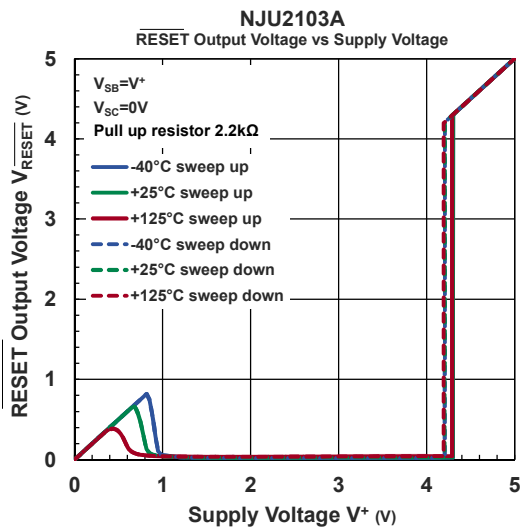
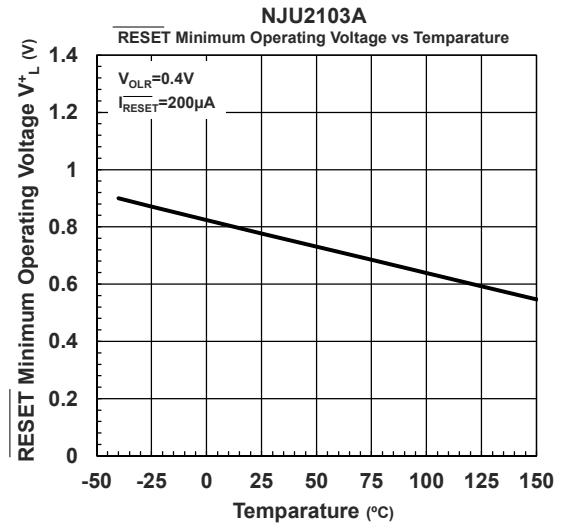
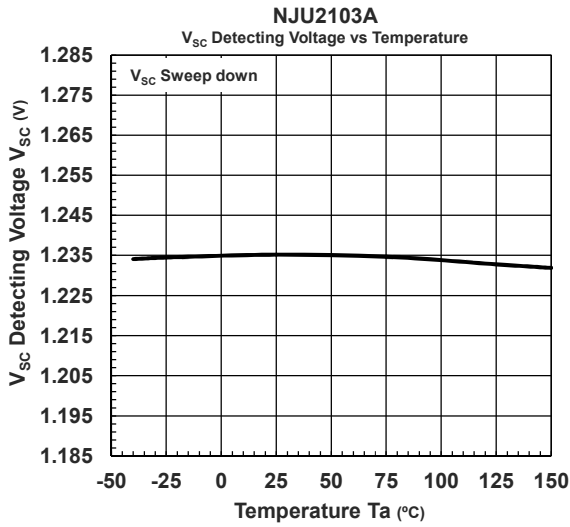
(4): Mounted on glass epoxy board.(76.2 x 114.3 x 1.6 :based on EIA/JEDEC standard, 4 Layers) internal Cu area: 74.2 x 74.2mm

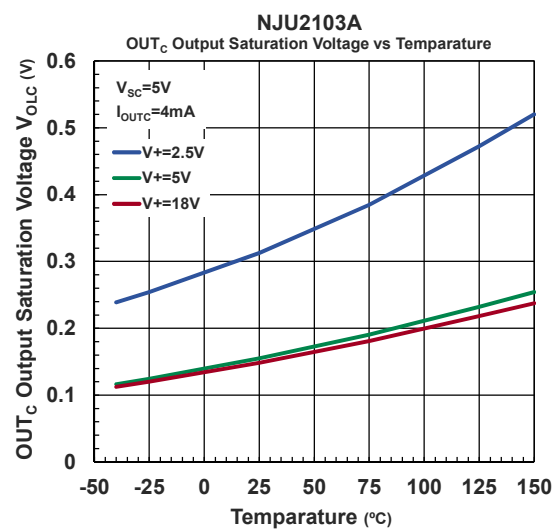
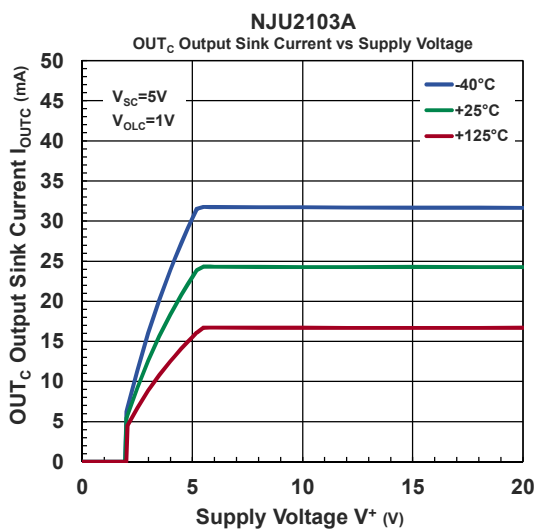
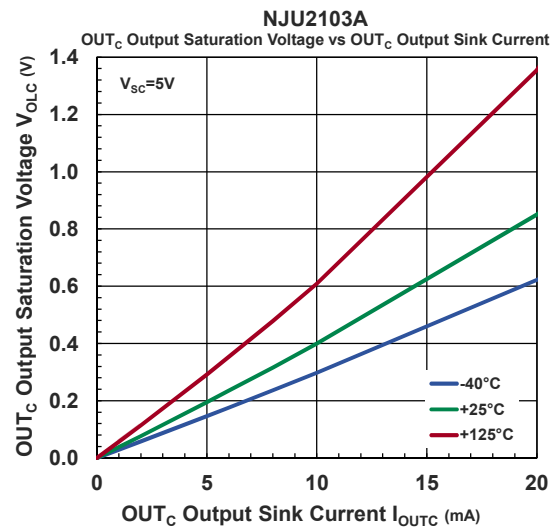
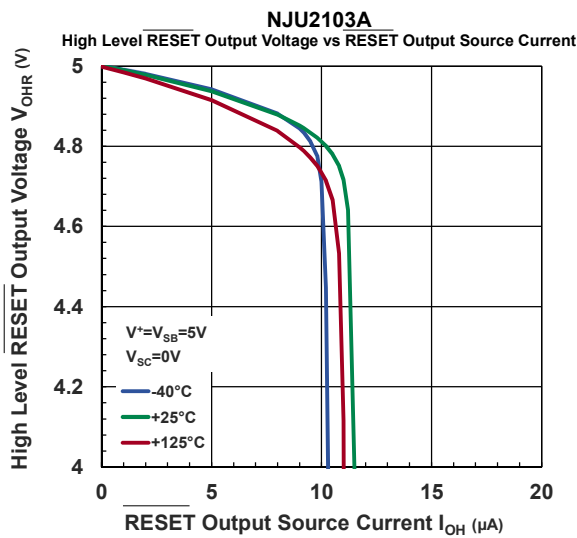
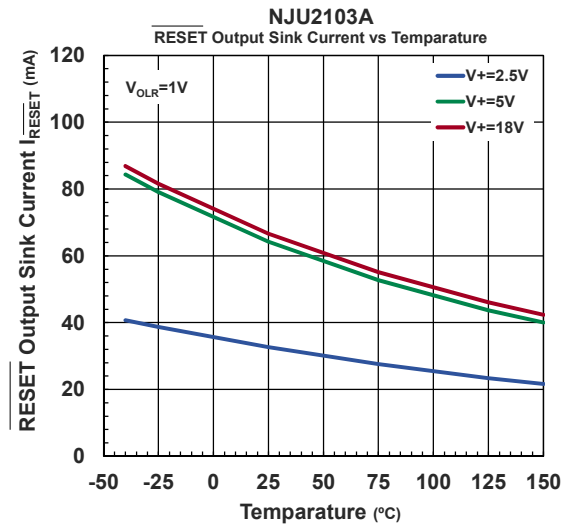
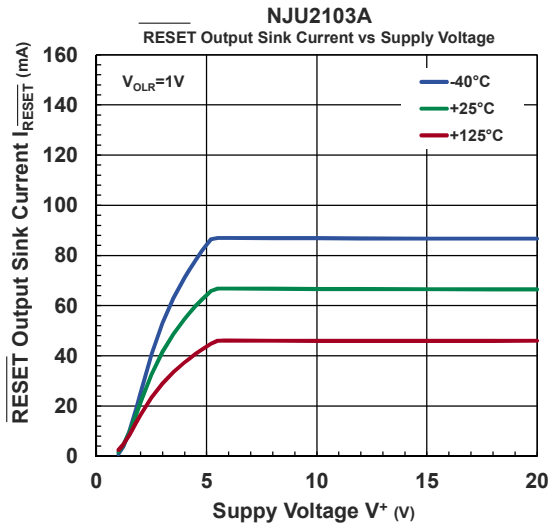
■ POWER DISSIPATION vs. AMBIENT TEMPERATURE

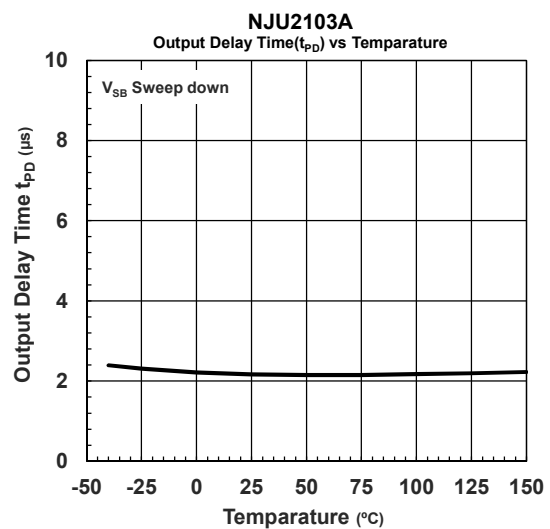
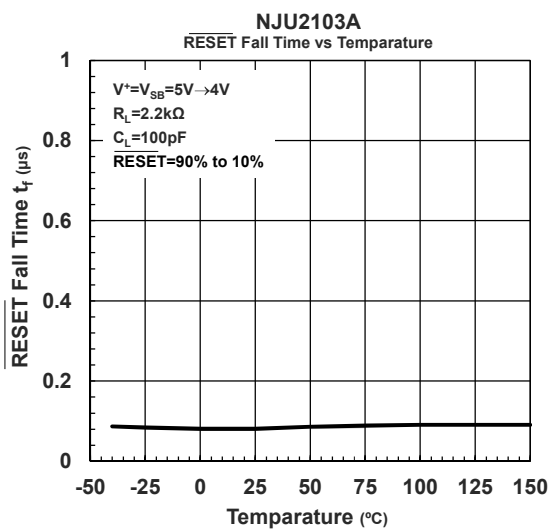
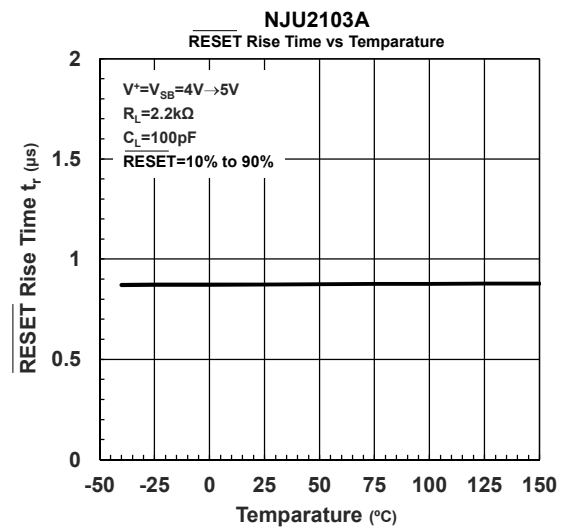
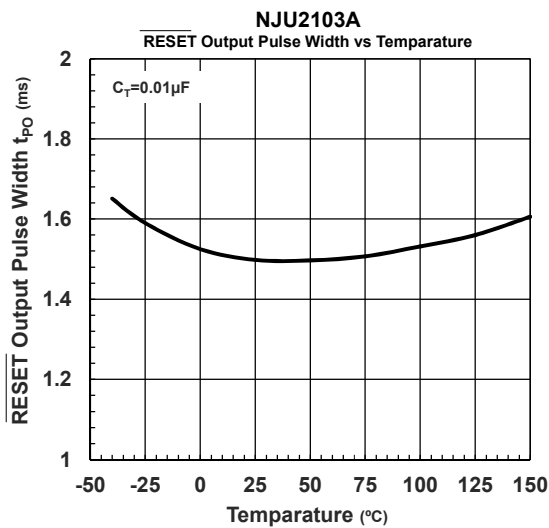
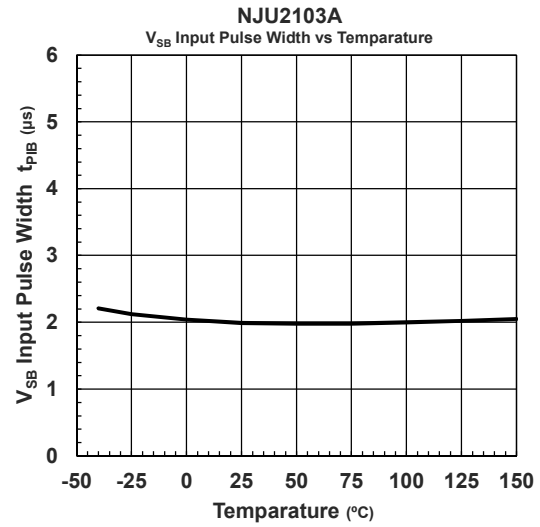
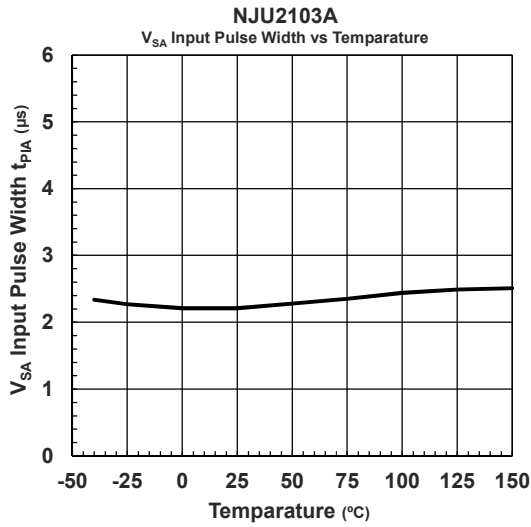


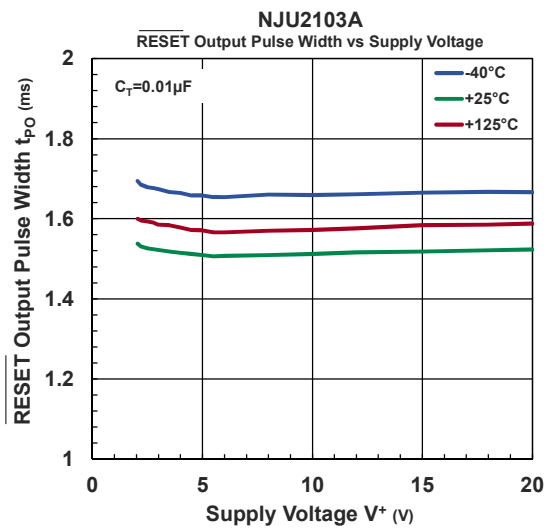
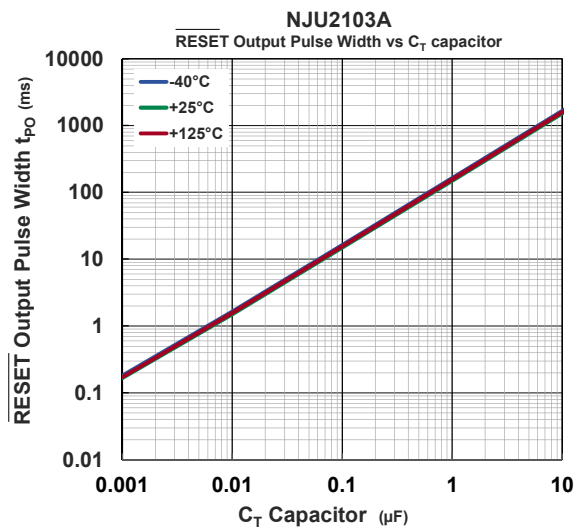
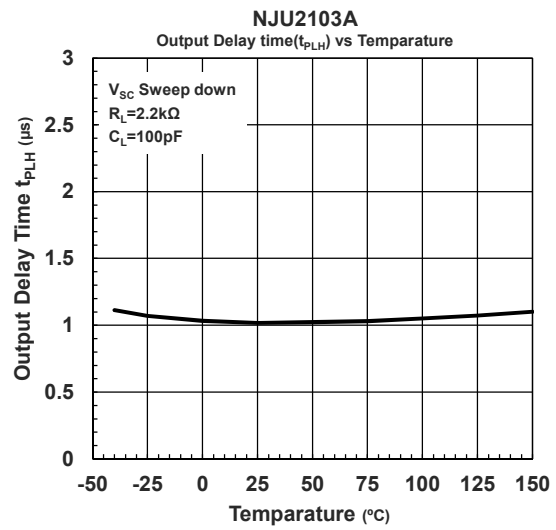
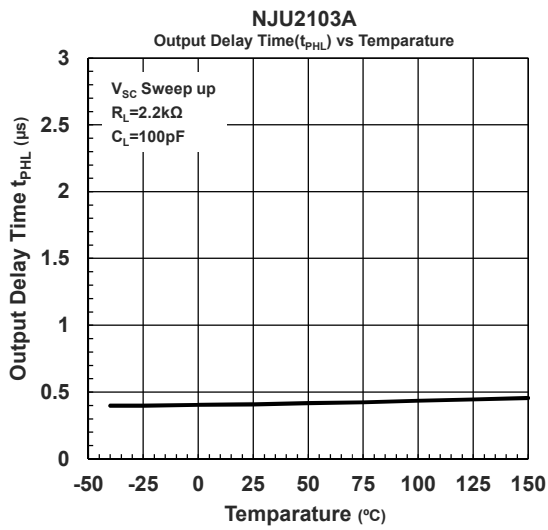
■ TYPICAL CHARACTERISTICS









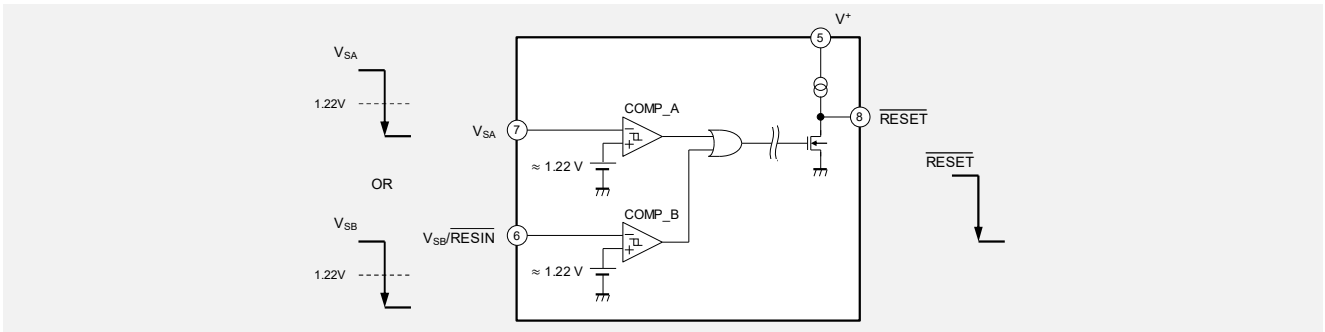


Technical Information

FUNCTION EXPLANATION

COMP_A and COMP_B are comparator with hysteresis in detection voltage.

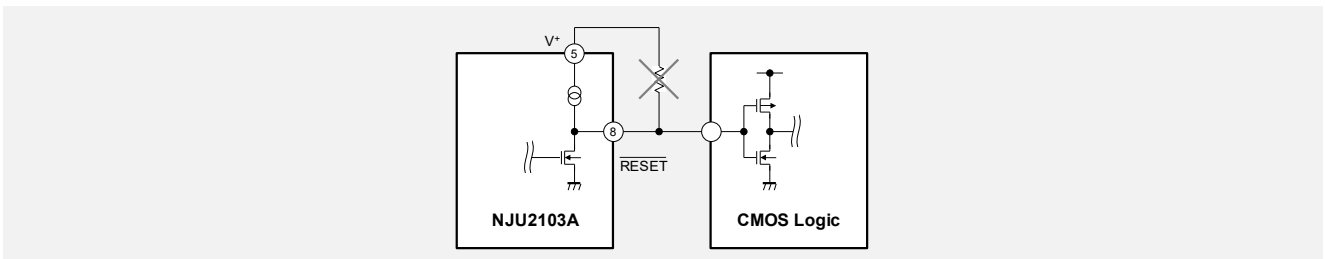
When either V_{SA} or V_{SB} pin voltage becomes about 1.22 V or less, the $\overline{RESET}$ output becomes "Low".



COMP_B can be used for arbitrary voltage detection (refer to Fig.3 or Fig.4) and also can be used as a manual reset function with reset hold time by TTL signal input. (refer to Fig.7)

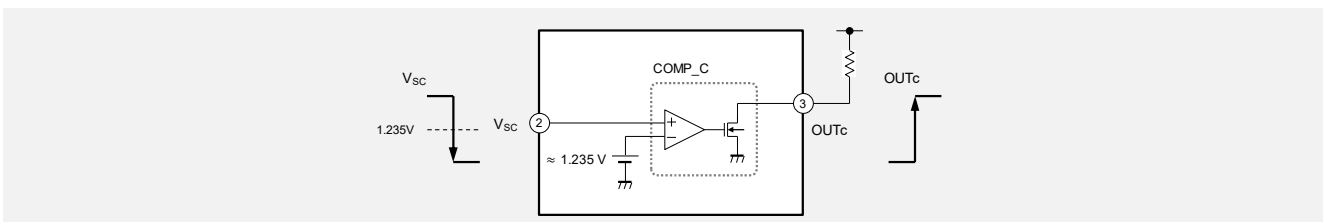
The NJU2103A can detect the instantaneous interruption and the instantaneous drop of the power line with a time of about 2 μ s width. If this level of instantaneous interruption or drop is not a problem, it can have a delayed trigger function by connecting capacitor to the V_{SA} and V_{SB} pins (refer to Fig.9).

Since the $\overline{RESET}$ pin is internally pulled up to V^+ , an external pull-up resistor isn't required in case of high impedance load like a CMOS logic IC.



COMP_C is an open-drain output comparator without hysteresis which has anti-polarity input and output.

Therefore, it can be used for overvoltage detection (refer to Fig. 14), positive logic reset output (refer to Fig.8) and generating a reference voltage source.(refer to Fig.11 to 13)

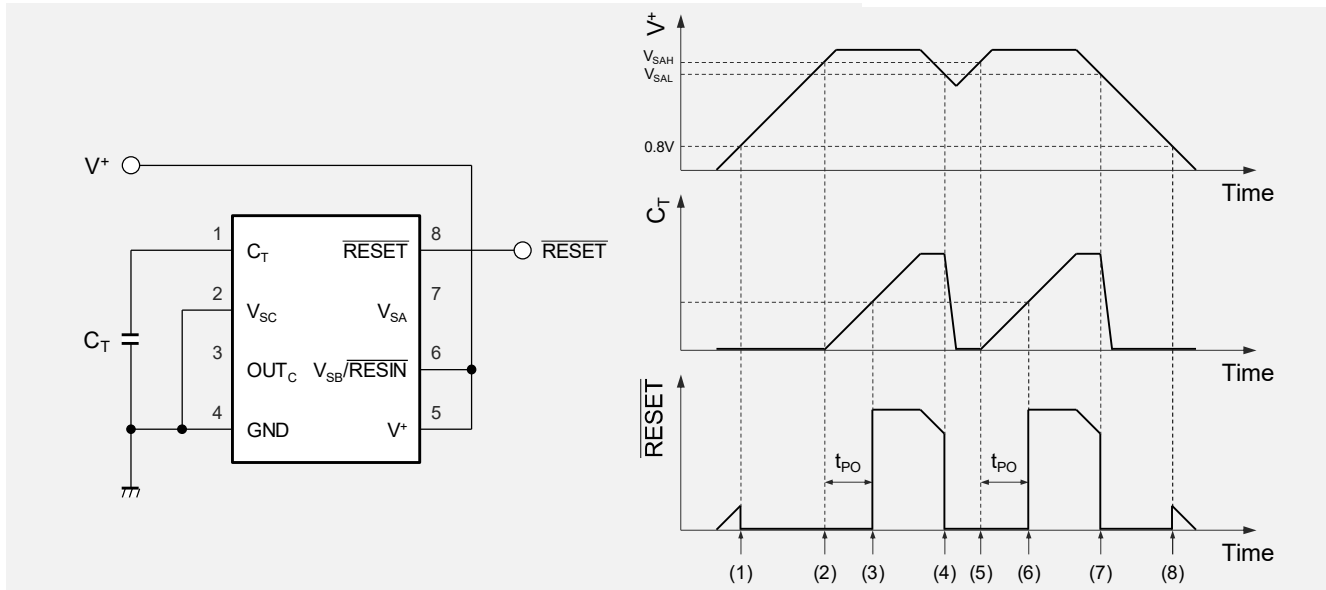


Unused Pin should be treated as shown in the table below.

Pin. No.	Pin Name	Treatment method of unused Pin
2	V_{SC}	Connect to GND
3	OUT_C	OPEN
6	$V_{SB}/\overline{RESIN}$	Connect to V^+
7	V_{SA}	OPEN
8	$\overline{RESET}$	OPEN

■ OPERATION EXPLANATION

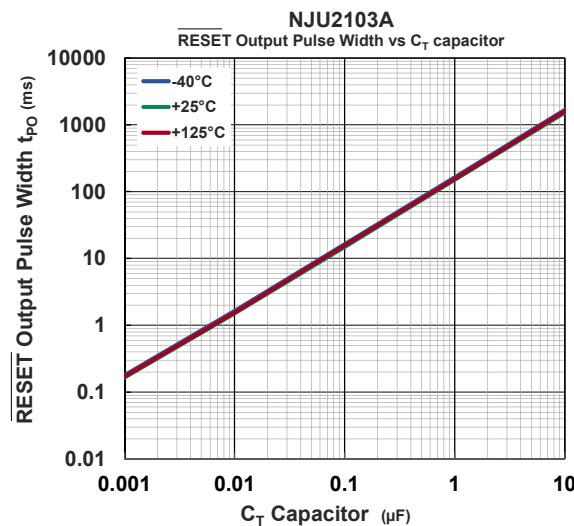
Technical Information



- (1) When V^+ increases to about 0.8V, $\overline{\text{RESET}}$ becomes Low
- (2) When V^+ increases to V_{SAH} , charging to capacitor C_T starts. At this time, $\overline{\text{RESET}}$ holds Low.
- (3) $\overline{\text{RESET}}$ switches from Low to High after the $\overline{\text{RESET}}$ Output Pulse Width t_{PO} .

Refer to "Output Pulse Width vs C_T capacitor" in TYPICAL CHARACTERISTICS and t_{PO} can be calculated as following formula.

$$\overline{\text{RESET}} \text{ Output Pulse Width } t_{PO} [\text{ms}] \approx 150 \times C_T [\mu\text{F}]$$



- (4) After $\overline{\text{RESET}}$ becomes High, When V^+ decreases below V_{SAL} , $\overline{\text{RESET}}$ goes Low and discharges C_T .
- (5) After V^+ decreases below V_{SAL} , it starts charging C_T when V^+ increase to V_{SAH} .
In case of instantaneous V^+ drop, if the time from V^+ decreases below V_{SAL} to increase to V_{SAH} is more than V_{SA} Input Pulse Width t_{PIA} , charging will start after discharging C_T .
- (6) V^+ increase to V_{SAH} and $\overline{\text{RESET}}$ switches from Low to High after $\overline{\text{RESET}}$ Output Pulse Width t_{PO}
- (7) When V^+ becomes less than V_{SAL} , repeat steps (4) – (6).
- (8) When V^+ decreases to 0 V, $\overline{\text{RESET}}$ holds Low until V^+ reaches about 0.8 V.

Technical Information

■APPLICATION EXAMPLE

1. 5V Power supply monitor

Monitor the 5V power supply with $V_{SA}(\text{COMP_A})$. The detection voltage at falling is the V_{SA} detection voltage 1 V_{SAL} (4.2 V typ.), and the detection voltage at rising is the V_{SA} detection voltage 2 V_{SAH} (4.3V typ.).

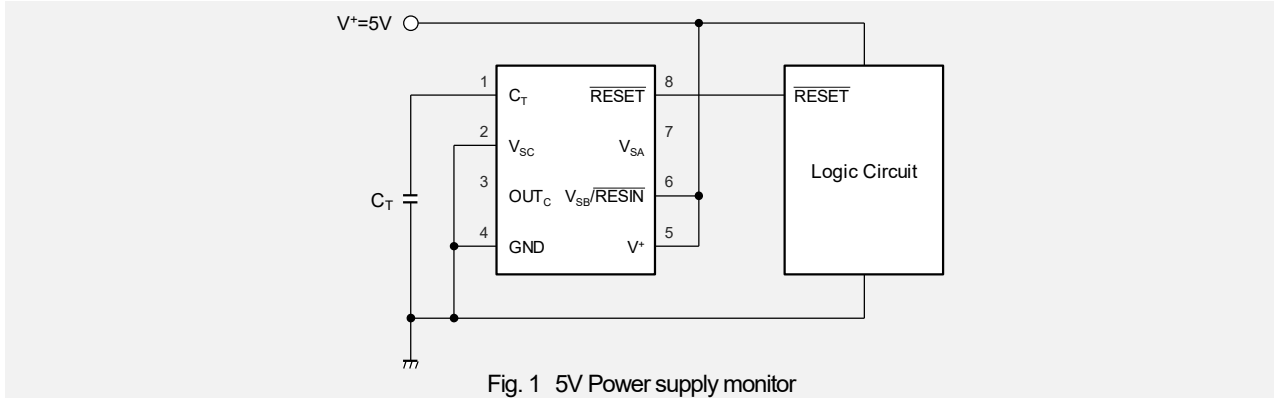


Fig. 1 5V Power supply monitor

2. Power supply monitor (adjust detection voltage by external resistor)

V_{SA} detection voltage1 can be adjusted with an external resistor.

- By selecting the external voltage-dividing resistors R_1 and R_2 to a sufficiently smaller value than internal voltage-dividing resistors R' , R'' (100 k Ω , 41 k Ω), the detection voltage can be set by the resistance ratio of R_1 and R_2 .

The formula for calculating detection voltage is as follows and refer to Tab.1 for setting example.

Detection voltage calculate formula ($R_1 \ll 100\text{k}\Omega$, $R_2 \ll 41\text{k}\Omega$)

$$\text{Detection Voltage(falling)} = \frac{(R_1 \parallel R') + (R_2 \parallel R'')}{R_2 \parallel R''} \times \frac{R''}{R' + R''} \times V_{SAL} \approx \frac{R_1 + R_2}{R_2} \times 1.2213 \text{ [V]}$$

$$\text{Detection Voltage(rising)} = \frac{(R_1 \parallel R') + (R_2 \parallel R'')}{R_2 \parallel R''} \times \frac{R''}{R' + R''} \times V_{SAH} \approx \frac{R_1 + R_2}{R_2} \times 1.2504 \text{ [V]}$$

Tab. 1 Setting example

External resistor R_1 [k Ω]	External resistor R_2 [k Ω]	Detection Voltage(falling) [V]	Detection Voltage(rising) [V]
6.2	2.4	4.37	4.47
12	5.1	4.11	4.20

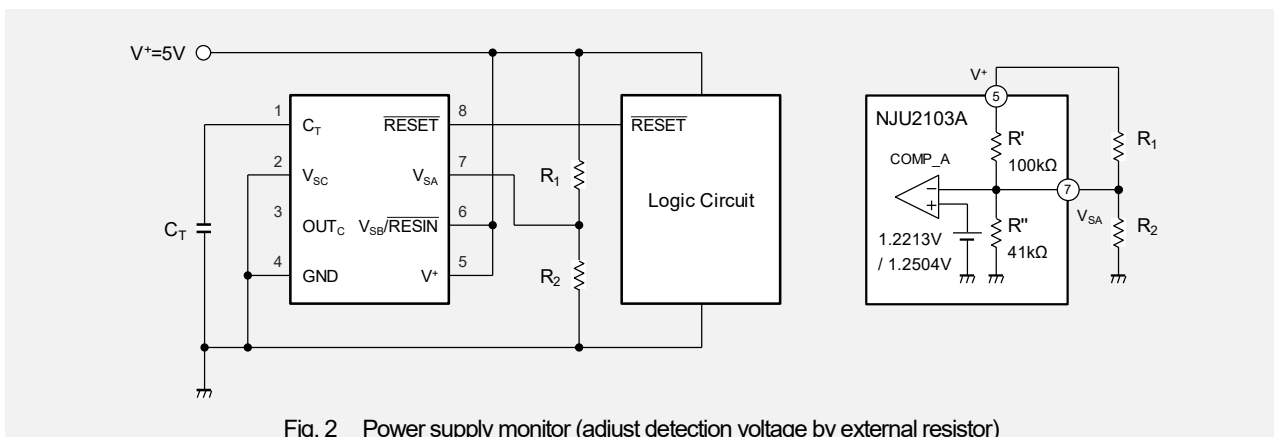


Fig. 2 Power supply monitor (adjust detection voltage by external resistor)

Technical Information

3. Arbitrary power supply monitor (monitoring $V^+ \leq 18V$)

Monitor the power supply of $V^+ \leq 18V$ with V_{SB} (COMP_B) and voltage-dividing resistors R_1 and R_2 .

- The detection voltage can be set by resistors R_1 and R_2 .

The formula for calculating R_1 and R_2 is as follows and refer to Tab.2.

Detection voltage calculate formula

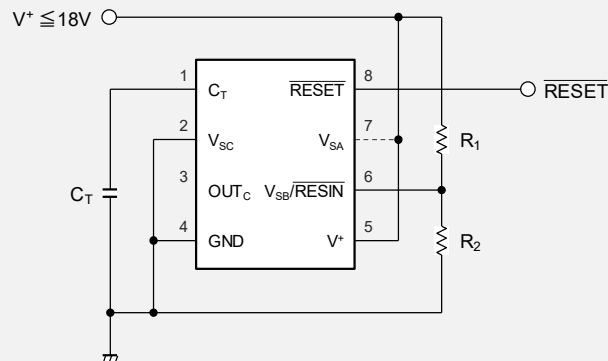
$$\text{Detection Voltage(falling)} = \frac{R_1 + R_2}{R_2} \times V_{SBL} \approx \frac{R_1 + R_2}{R_2} \times 1.220 \text{ [V]}$$

$$\text{Detection Voltage(rising)} = \frac{R_1 + R_2}{R_2} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_1 + R_2}{R_2} \times 1.248 \text{ [V]}$$

- When V^+ is 4.45V or less, connects V_{SA} (pin 7) to V^+ to disable COMP_A
- When V^+ is greater than 4.45 V, V_{SA} (pin 7) should be opened. And in this case, current consumption decreases. (decrease value: $17.3 \times V^+ \text{ [}\mu\text{A]}$)

Tab. 2 setting example

External resistor R_1 [kΩ]	External resistor R_2 [kΩ]	Detection Voltage(falling) [V]	Detection Voltage(rising) [V]
43	16	4.50	4.60
22	15	3.01	3.08

Fig. 3 Arbitrary power supply monitor (monitoring $V^+ \leq 18V$)

Technical Information

4. Arbitrary power supply monitor (monitoring $V^+ > 18V$)

Monitor the power supply of $V^+ > 18V$ with V_{SB} (COMP_B) and voltage-dividing resistors R_1 and R_2 .

The power supply of this IC (about 5V) is generated with V_{SC} (COMP_C) and feedback resistors R_4 and R_5 .

- Set the detection voltage with resistors R_1 and R_2 according to the following formula.

Detection voltage calculate formula

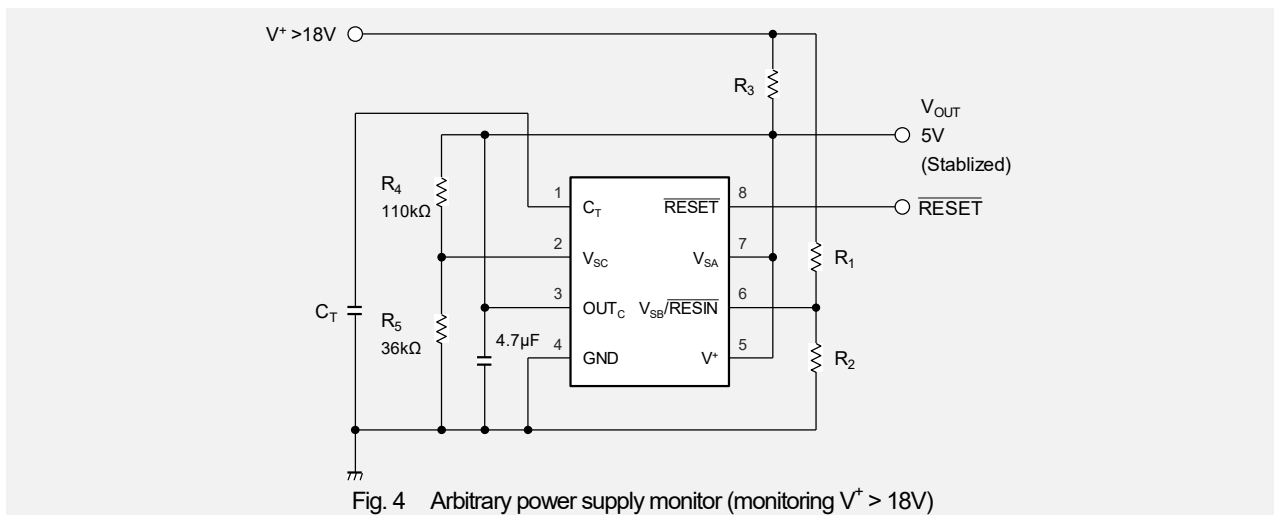
$$\text{Detection Voltage}(V^+ \text{ falling}) = \frac{R_1 + R_2}{R_2} \times V_{SBL} \approx \frac{R_1 + R_2}{R_1} \times 1.220 \text{ [V]}$$

$$\text{Detection Voltage}(V^+ \text{ rising}) = \frac{R_1 + R_2}{R_2} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_1 + R_2}{R_2} \times 1.248 \text{ [V]}$$

- The $\overline{\text{RESET}}$ output is $\approx 0V$ (low level) and $\approx 5V$ (high level). Not outputs V^+ voltage.
 $\overline{\text{RESET}}$ should not be pulled up to V^+
- If the resistor ratio of R_4 and R_5 is adjusted, high level $\overline{\text{RESET}}$ voltage is changed according to constant voltage set by resistor ratio of R_4 and R_5 . Constant voltage V_{OUT} is calculated as the following formula. However, shouldn't be exceed 18V.

$$\text{Constant Voltage } V_{OUT} = \frac{R_4 + R_5}{R_5} \times V_{SC} \approx \frac{R_4 + R_5}{R_5} \times 1.235 \text{ [V]}$$

- The constant voltage (5V output) can be used as the power supply for the small current consumption circuit.
- When deciding the value of R_3 , it is necessary to be careful about power consumption.



Technical Information

5. 5V, 12V power supply monitor (dual power supply monitor e.g. $V_1^+ = 5V$, $V_2^+ = 12V$)

Monitor the V_1^+ (5V) power supply with V_{SA} (COMP_A) and monitor the V_2^+ (12V) power supply with V_{SB} (COMP_B) and voltage-dividing resistors R_1 and R_2 .

- V_1^+ detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.
- V_2^+ detection voltage (falling, rising) is set by R_1 and R_2 according to following formula. In case of resistor value in Fig.5, the detection voltage (falling) is about 9.0 V and the detection voltage (rising) is about 9.2 V.

 V_2^+ detection voltage calculate formula

$$\text{Detection Voltage}(V_2^+ \text{ falling}) = \frac{R_1 + R_2}{R_2} \times V_{SBL} \approx \frac{R_1 + R_2}{R_2} \times 1.220 \text{ [V]}$$

$$\text{Detection Voltage}(V_2^+ \text{ rising}) = \frac{R_1 + R_2}{R_2} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_1 + R_2}{R_2} \times 1.248 \text{ [V]}$$

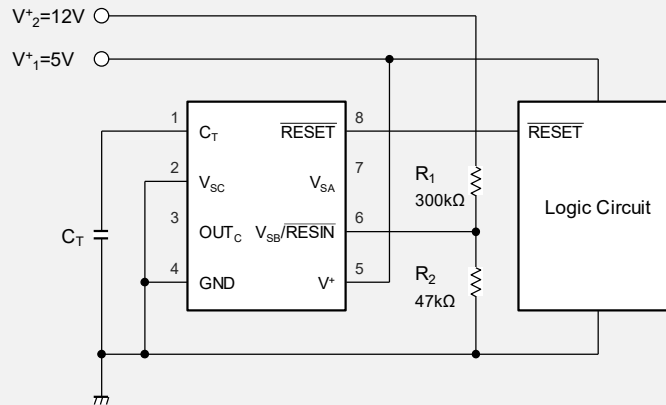


Fig. 5 5V, 12V power supply monitor (dual power supply monitor : $V_1^+ = 5V$, $V_2^+ = 12V$)

Technical Information

6. 5V, 12V power supply monitor (e.g. $V_1^+ = 5V$, $V_2^+ = 12V$, $\overline{\text{RESET}}$ output is only V_1^+ detection result)

Monitor the $V_1(5V)$ power supply with $V_{SA}(COMP A)$ and output signal from $\overline{RESET}$.

In addition, monitor the V_2 (12V) power supply with $V_{SC}(\text{COMP_C})$ and voltage-dividing resistors R_1 , R_2 , R_3 , R_4 , NPN transistor., base current limiting resistor R_5 , and output signal from OUT_C .

- V_1^+ detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.
- V_2^+ detection voltage (falling) and hysteresis width at rising are calculated as following formula. In case of resistor value in Fig.6, the detection voltage (falling) is about 9.0 V and the hysteresis width at rising is about 0.2 V

V₂ detection voltage and hysteresis width at rising calculate formula

$$\text{Detection Voltage}(V_2^+ \text{falling}) = \frac{R_1 + R_2 + R_3}{R_2 + R_3} \times V_{sc} \approx \frac{R_1 + R_2 + R_3}{R_2 + R_3} \times 1.235 \text{ [V]}$$

$$\text{Hysteresis width at rising} = \frac{R_1(R_3 - R_3 \parallel R_4)}{(R_2 + R_3)(R_2 + R_3 \parallel R_4)} \times V_{SC} \approx \frac{R_1(R_3 - R_3 \parallel R_4)}{(R_2 + R_3)(R_2 + R_3 \parallel R_4)} \times 1.235 \text{ [V]}$$

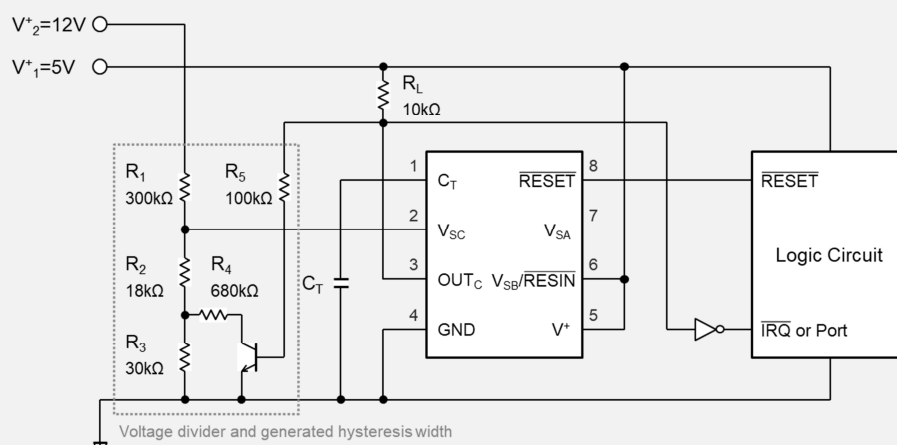


Fig. 6 5V, 12V power supply monitor ($V_1^+ = 5V$, $V_2^+ = 12V$, $\overline{\text{RESET}}$ output is only V_1^+ detection result)

7. Manual Reset function ($V^+ = 5V$)

By inputting the TTL signal to $V_{SP}/\overline{RESIN}$, it realizes manual reset output signal regardless of the state of V^+ .

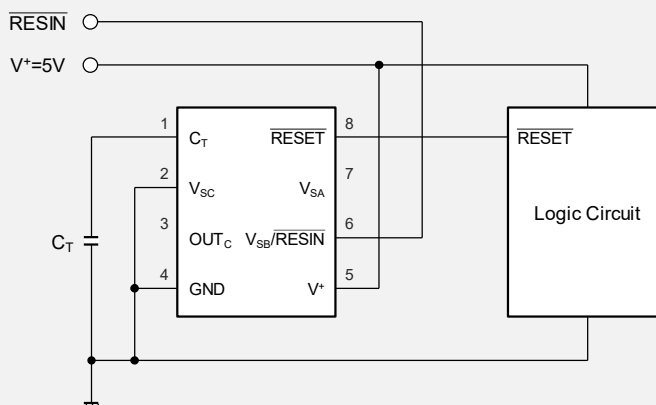


Fig. 7 Manual Reset function ($V^+ = 5V$)

Technical Information

8. Non-inverting reset output

If a positive output is required for reset signal, invert the $\overline{\text{RESET}}$ output with COMP_C and output from OUT_C. Since OUT_C is an open drain output, It is required the pull-up resistor.(shown as R_L in Fig.8)

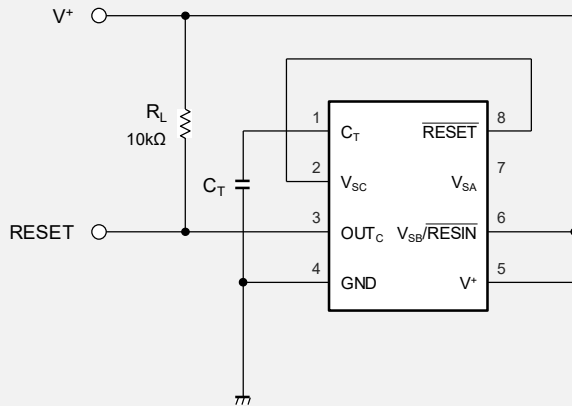


Fig. 8 Non-inverting reset output

9. Power supply voltage monitoring by delayed trigger

An arbitrary delay is added to the COMP_A operation by connecting capacitor C₁ between V_{SA} and GND.

When C₁ is connected minimum input pulse width becomes longer. E.g. t_{PI} = 40μs (C₁=1000pF)

Minimum input pulse width t_{PI} is calculated as following formula.

Minimum input pulse width calculate formula

$$t_{PI} [\mu s] \approx (R' \parallel R'') \times \ln \left(\frac{5 - 4}{V_{SAL} - 4} \right) \times 10^{-6} \times C_1 [pF] \approx 4.7 \times 10^{-2} \times C_1 [pF]$$

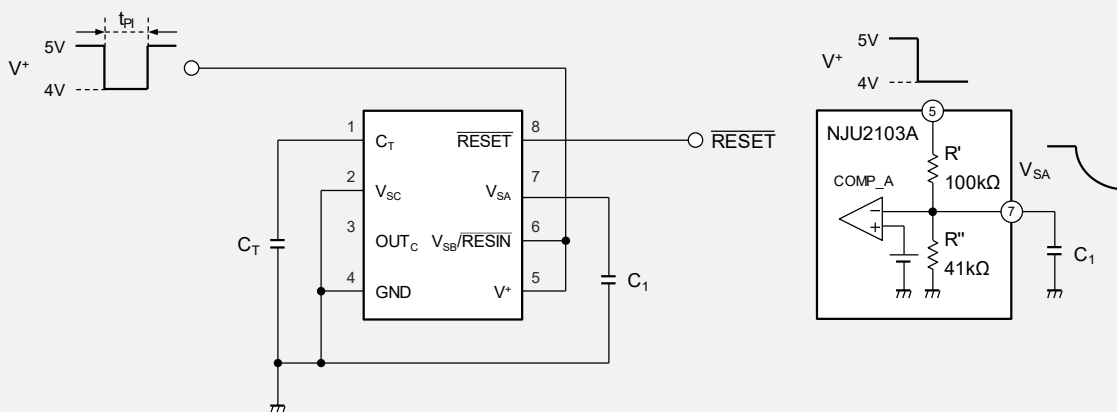


Fig. 9 Power supply voltage monitoring by delayed trigger

Technical Information

10. Positive and negative dual power supply monitoring (e.g. $V^+ = 5V$, V^- =negative voltage)

Monitor the positive power supply with V_{SA} (COMP_A) and monitor the negative voltage with V_{SB} (COMP_B)

V_{SC} (COMP_C) is used to shift negative voltage to positive voltage.

- R_1 , R_2 , R_3 should have the same resistance value
- V^+ detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.
- V^- detection voltage is calculated as following formula. In case of resistor value in Fig.10, the detection voltage (falling) is about -4.3V and the detection voltage (rising) is about -4.4V.

 V^- detection voltage calculate formula

$$\text{Detection voltage } (V^- \text{ falling}) = \frac{R_3 + R_4}{R_3} \times V_{SC} - \frac{2R_4}{R_3} \times V_{SBL} \approx \frac{R_3 - R_4}{R_3} \times 1.220 \text{ [V]}$$

$$\text{Detection voltage } (V^- \text{ rising}) = \frac{R_3 + R_4}{R_3} \times V_{SC} - \frac{2R_4}{R_3} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_3 - R_4}{R_3} \times 1.248 \text{ [V]}$$

- When using a power supply that outputs V^- without V^+ output, it is necessary to connect a Schottky barrier diode (SBD) between the V_{SC} and GND to prevent being applied negative voltage to this IC.

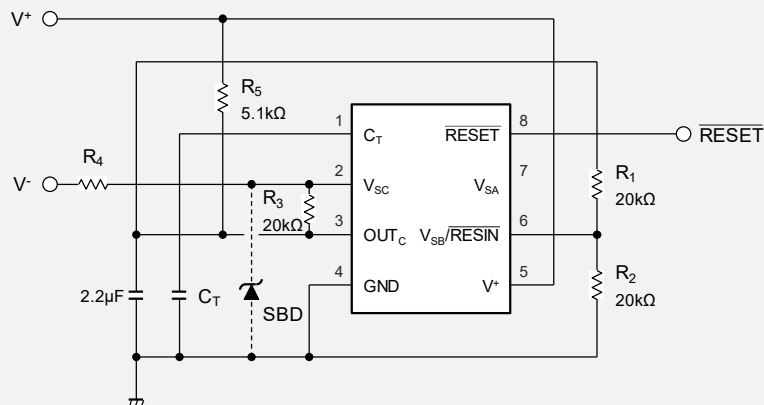


Fig. 10 Positive and negative dual power supply monitoring ($V^+ = 5V$, V^- =negative voltage)

Technical Information

11. Reference voltage output and voltage drop monitoring (e.g. 9V reference output, 5V, 9V monitoring)

Monitor the V^+ (5V) power supply with $V_{SA}(COMP_A)$.

9V Reference voltage V_{OUT} is generated by $V_{SC}(COMP_C)$, feedback resistors R_3 , R_4 and NPN transistor, and its 9V is monitored by $V_{SB}(COMP_B)$ and voltage-dividing resistors R_1 and R_2 .

- V^+ detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.
- The reference voltage V_{OUT} and its detection voltage are calculated as the following formula. In case of resistor value in Fig.11, the reference voltage V_{OUT} is about 9.0V, the detection voltage (V_{OUT} falling) is about 7.1V and the detection voltage (V_{OUT} rising) is about 7.3V

Reference Voltage and detection voltage calculate formula

$$\text{Reference voltage } V_{OUT} = \frac{R_3 + R_4}{R_4} \times V_{SC} \approx \frac{R_3 + R_4}{R_4} \times 1.235 \text{ [V]}$$

$$\text{Detection Voltage}(V_{OUT} \text{ falling}) = \frac{R_1 + R_2}{R_2} \times V_{SBL} \approx \frac{R_1 + R_2}{R_2} \times 1.220 \text{ [V]}$$

$$\text{Detection Voltage}(V_{OUT} \text{ rising}) = \frac{R_1 + R_2}{R_2} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_1 + R_2}{R_2} \times 1.248 \text{ [V]}$$

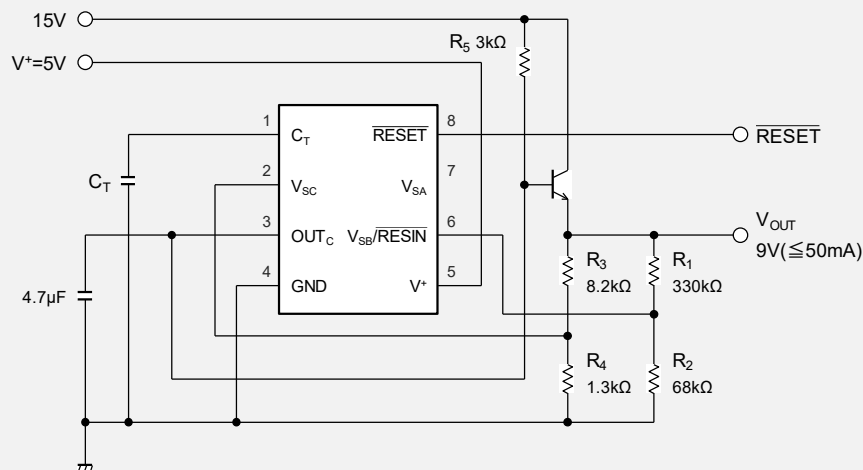


Fig. 11 Reference voltage output and voltage drop monitoring (e.g. 9V reference output, 5V, 9V monitoring)

Technical Information

12-1. Reference Voltage output and Voltage drop monitoring (e.g. 5V output, 5V monitoring)

5V Reference voltage V_{OUT} is generated by $V_{SC}(COMP_C)$, feedback resistors R_3 , R_4 , NPN transistor and drive resistor R_5 , and its 5V is monitored by $V_{SA}(COMP_A)$.

- The reference voltage V_{OUT} is calculated as following formula. In case of resistor value In Fig.12-1, the reference voltage V_{OUT} is about 5.0V

Reference Voltage calculate formula

$$\text{Reference voltage } V_{OUT} = \frac{R_3 + R_4}{R_3} \times V_{SC} \approx \frac{R_3 + R_4}{R_3} \times 1.235 \text{ [V]}$$

- The detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.

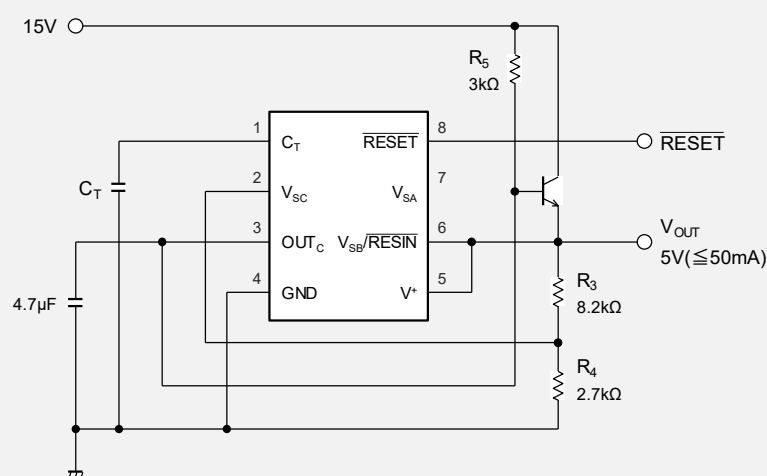


Fig. 12-1 Reference Voltage output and Voltage drop monitoring (e.g. 5V output, 5V monitoring)

Technical Information

12-2. Reference Voltage output and Voltage drop monitoring (e.g. 5V output, 5V monitoring)

5V Reference voltage V_{OUT} is generated by $V_{SC}(COMP_C)$ and feedback resistors R_2 , R_3 , and its 5V is monitored by $V_{SA}(COMP_A)$. Unlike Fig.12-1, 5V output cannot supply large current.

- The reference voltage V_{OUT} is calculated as following formula.

In case of resistor value In Fig.12-2, the reference voltage V_{OUT} is about 5.0V

$$\text{Reference voltage } V_{OUT} = \frac{R_2 + R_3}{R_3} \times V_{SC} \approx \frac{R_2 + R_3}{R_3} \times 1.235 \text{ [V]}$$

- The detection voltage (falling) is 4.2V and detection voltage (rising) is 4.3V.
- R_1 value should be calculated from current consumption of NJU2103A, the current flowing through R_2 and R_3 , and 5V output current. .

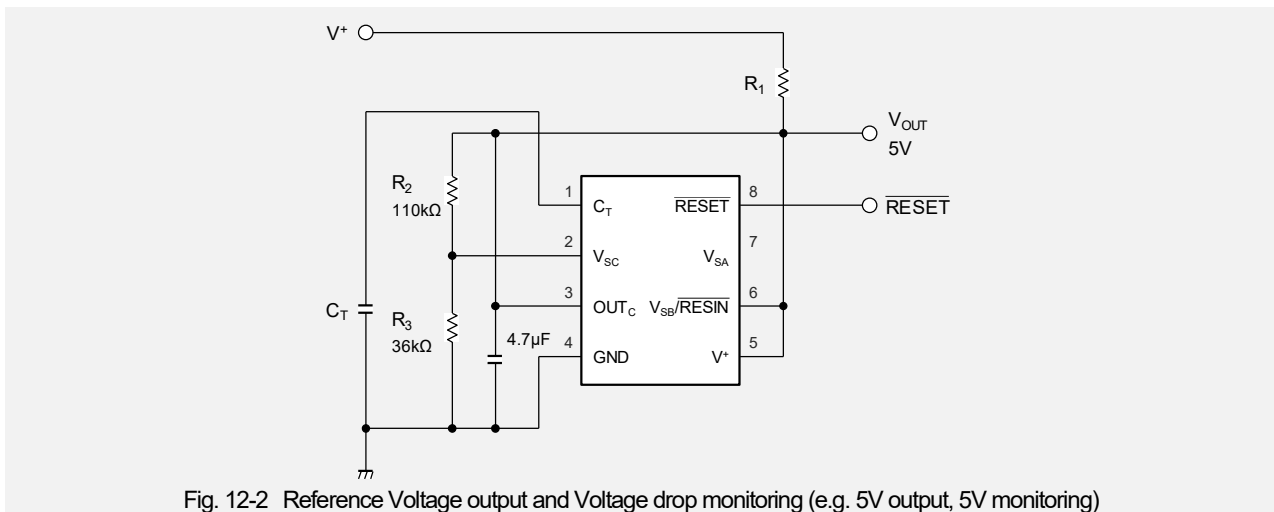


Fig. 12-2 Reference Voltage output and Voltage drop monitoring (e.g. 5V output, 5V monitoring)

13. Reference Voltage output and Voltage drop monitoring (e.g. 1.235V output, 5V monitoring)

Buffer-connect the $V_{SC}(COMP_C)$ and output the reference voltage of $COMP_C$.

The output current of the reference voltage output is limited by R_1 . If R_1 is 1.2 kΩ, it can output about 2 mA

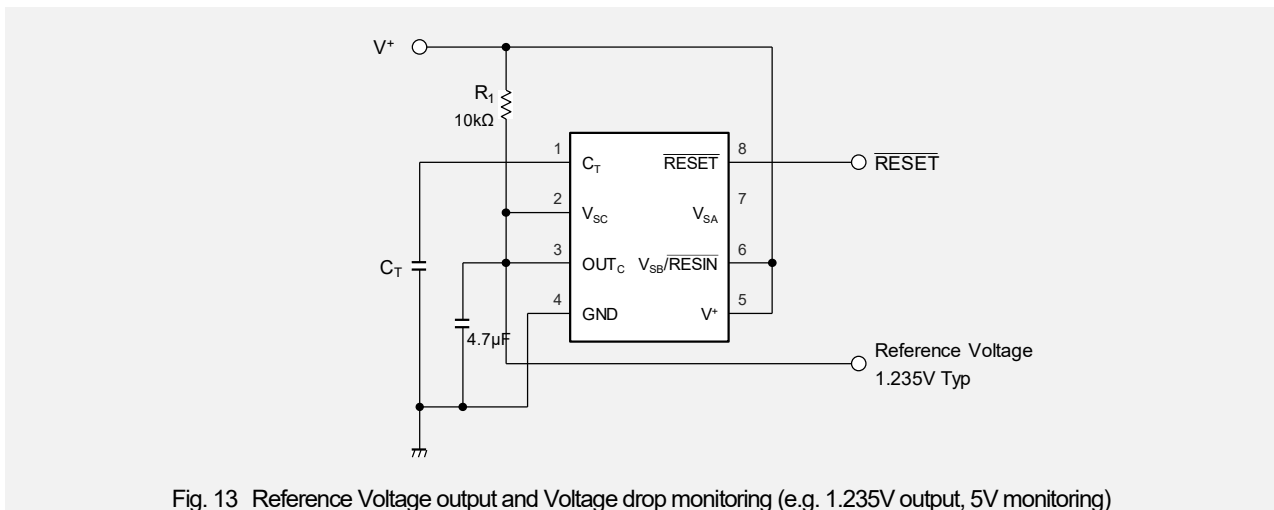


Fig. 13 Reference Voltage output and Voltage drop monitoring (e.g. 1.235V output, 5V monitoring)

Technical Information

14. Low voltage and over voltage detection ($V^+ = 5V$)

V_{SB} (COMP_B) for low voltage detection and V_{SC} (COMP_C) for overvoltage detection.

Logically synthesizes low voltage and over voltage detection by connecting OUT_C to V_{SA} , and output from $\overline{RESET}$.

- Low voltage detection and over voltage detection are calculated as following formula.

$$\text{Low voltage detection (falling)} V_{SL1} = \frac{R_1 + R_2}{R_2} \times V_{SBL} \approx \frac{R_1 + R_2}{R_2} \times 1.220 \text{ [V]}$$

$$\text{Low voltage detection (rising)} V_{SL2} = \frac{R_1 + R_2}{R_2} \times (V_{SBL} + V_{HRSB}) \approx \frac{R_1 + R_2}{R_2} \times 1.248 \text{ [V]}$$

$$\text{Over voltage detection } V_{SH} = \frac{R_3 + R_4}{R_4} \times V_{SC} \approx \frac{R_3 + R_4}{R_4} \times 1.235 \text{ [V]}$$

- There is no hysteresis characteristics for over voltage detection.
- " $\overline{RESET}$ Output Pulse Width t_{PO} " is valid even when overvoltage is detected

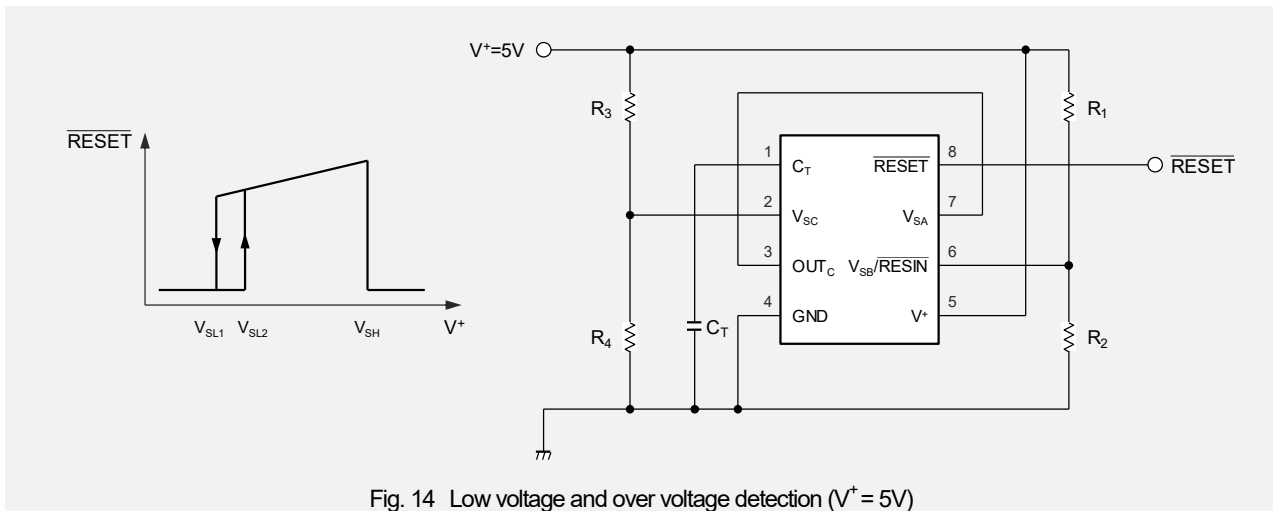
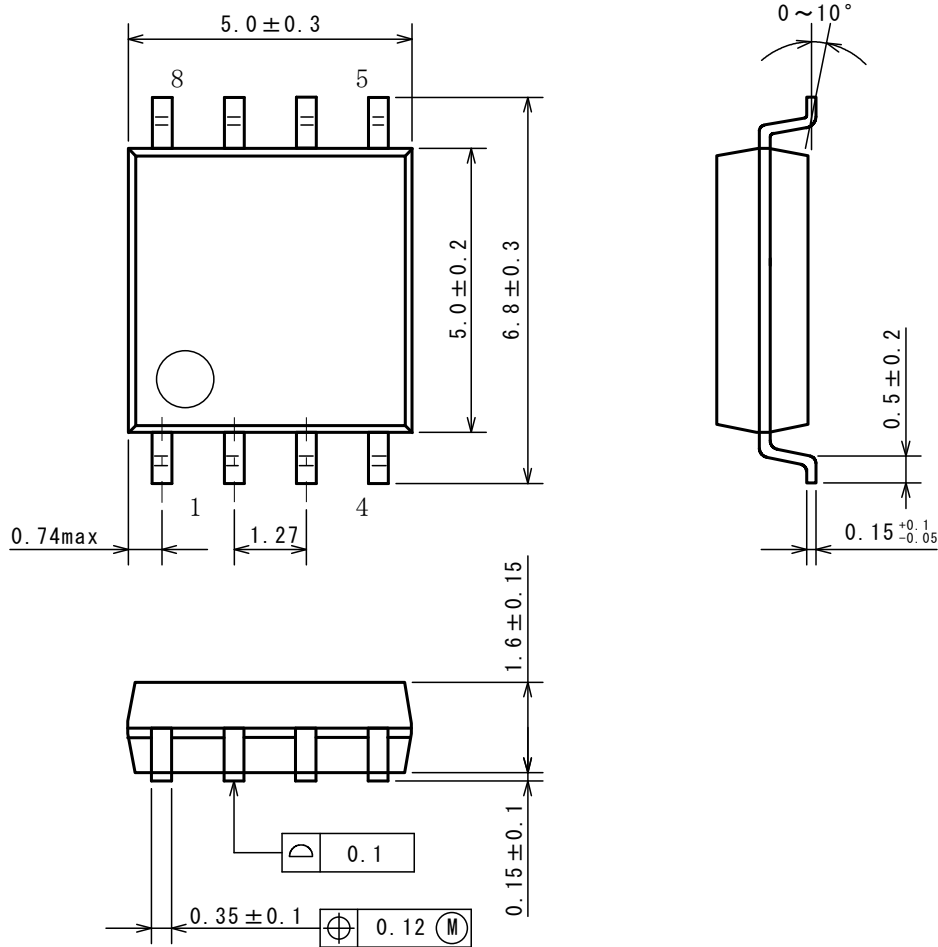
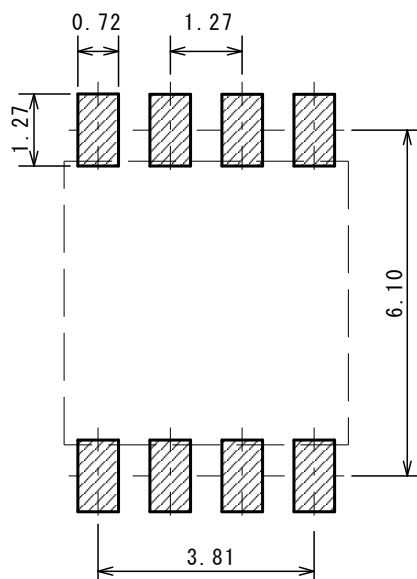


Fig. 14 Low voltage and over voltage detection ($V^+ = 5V$)

■PACKAGE DIMENSIONS



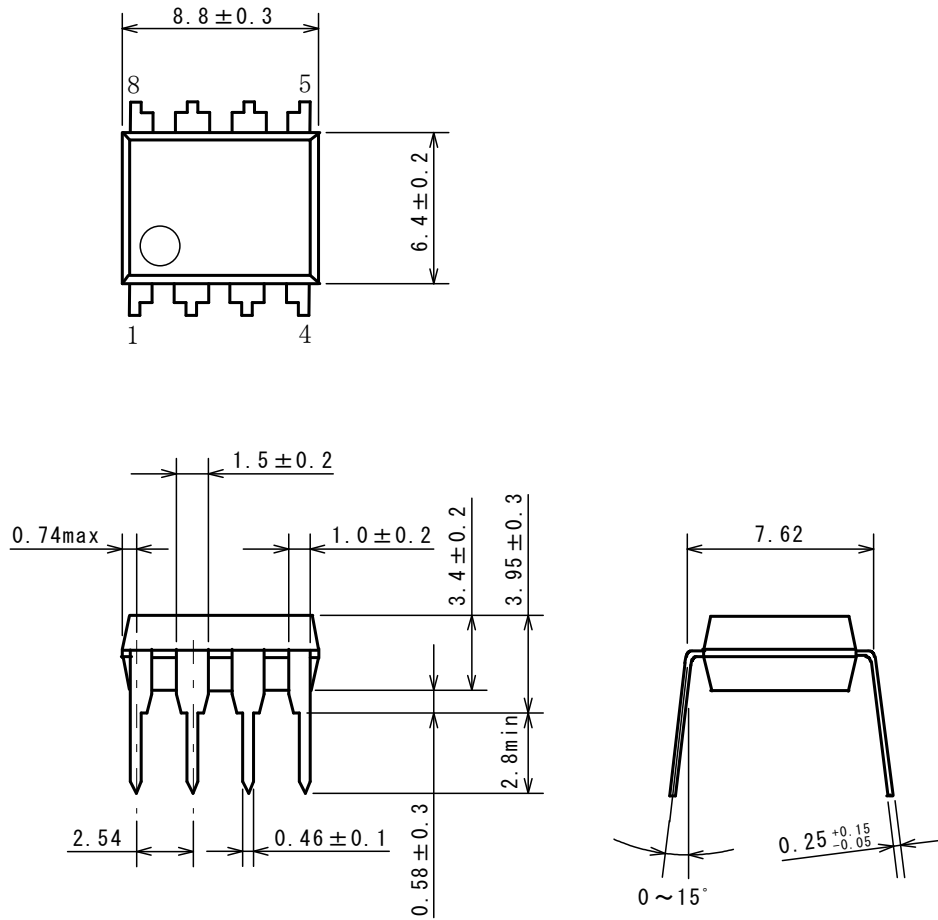
■EXAMPLE OF SOLDER PADS DIMENSIONS



■PACKAGE DIMENSIONS

DIP8

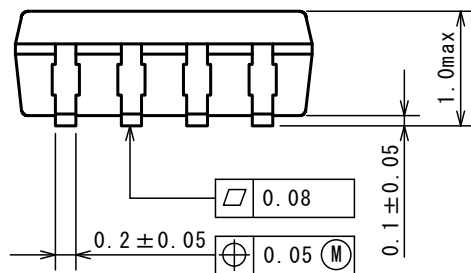
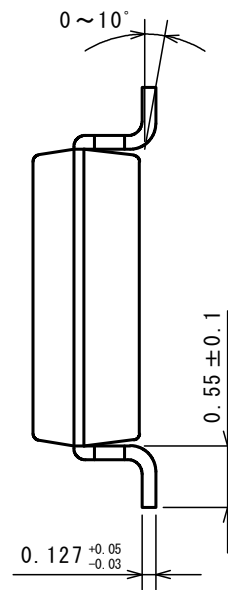
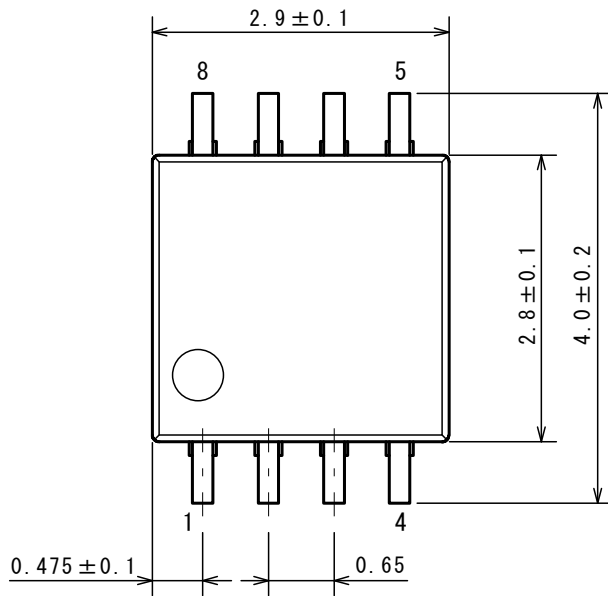
Unit: mm



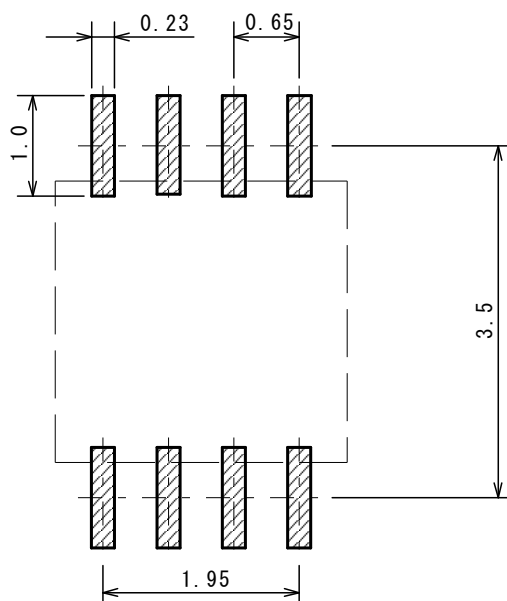
TVSP8(MSOP8) MEET JEDEC MO-187-DA/THIN TYPE

■PACKAGE DIMENSIONS

Unit: mm

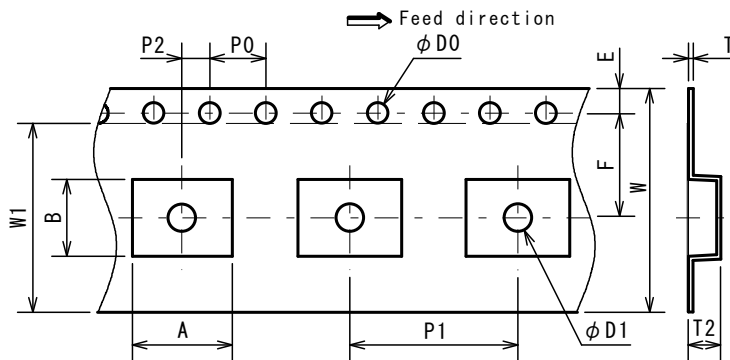


■EXAMPLE OF SOLDER PADS DIMENSIONS



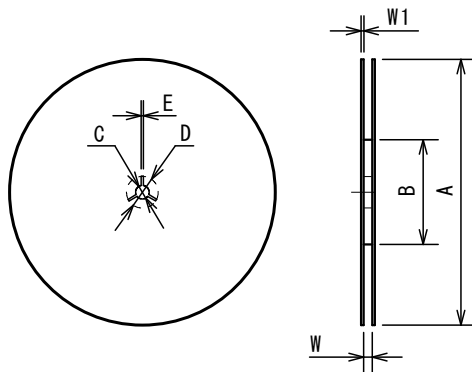
PACKING SPEC

TAPING DIMENSIONS



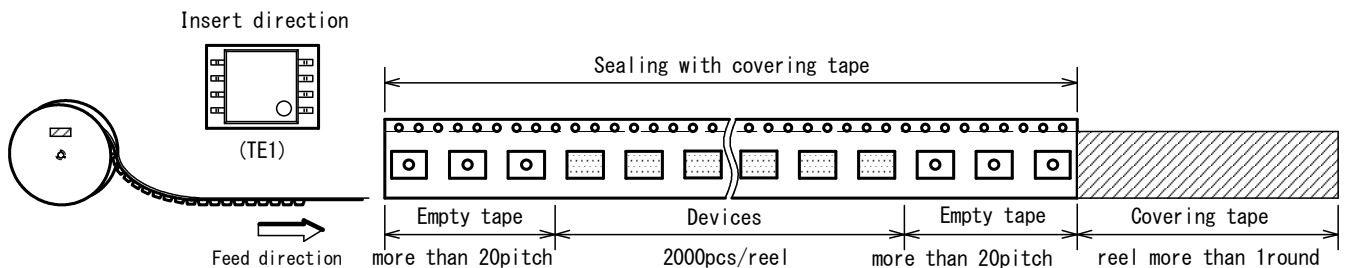
SYMBOL	DIMENSION	REMARKS
A	7.1	BOTTOM DIMENSION
B	5.4	BOTTOM DIMENSION
D0	1.55 ± 0.05	
D1	2.05 ± 0.1	
E	1.75 ± 0.1	
F	7.5 ± 0.1	
P0	4.0 ± 0.1	
P1	12.0 ± 0.1	
P2	2.0 ± 0.1	
T	0.3 ± 0.05	
T2	2.3	
W	16.0 ± 0.3	
W1	13.5	THICKNESS 0.1max

REEL DIMENSIONS

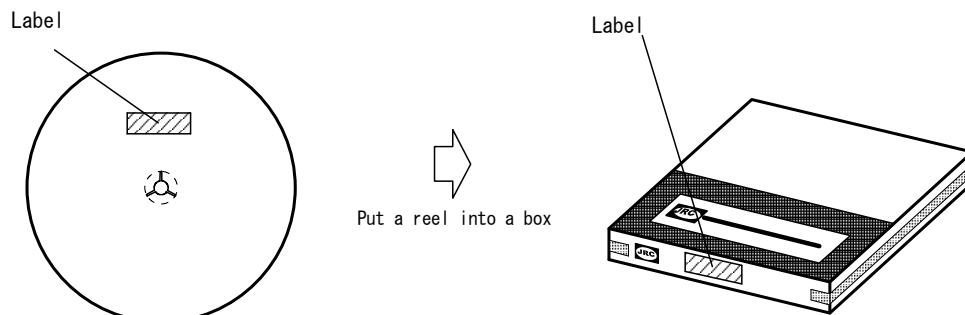


SYMBOL	DIMENSION
A	$\phi 330 \pm 2$
B	$\phi 80 \pm 1$
C	$\phi 13 \pm 0.2$
D	$\phi 21 \pm 0.8$
E	2 ± 0.5
W	17.5 ± 0.5
W1	2 ± 0.2

TAPING STATE



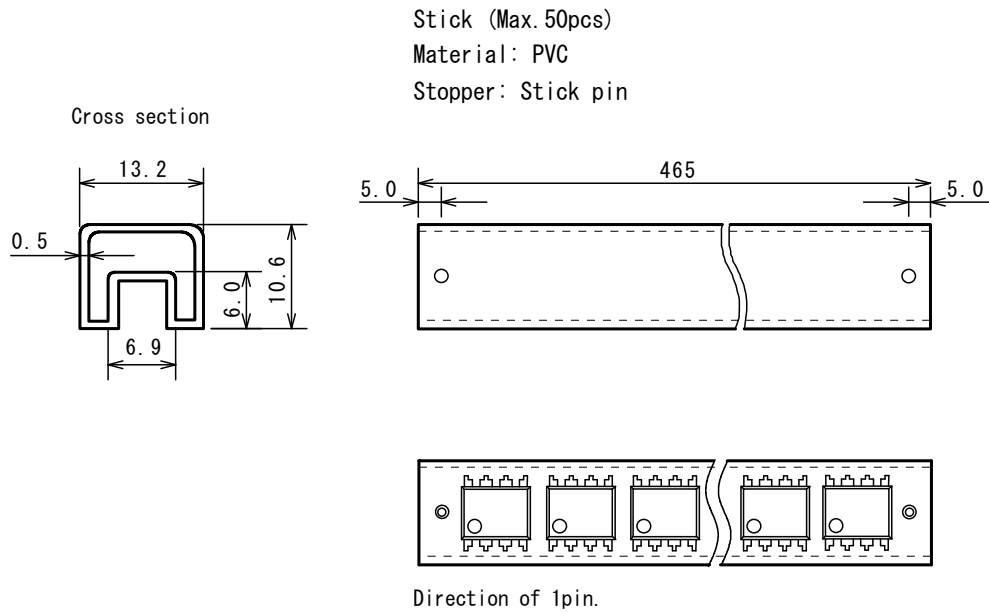
PACKING STATE



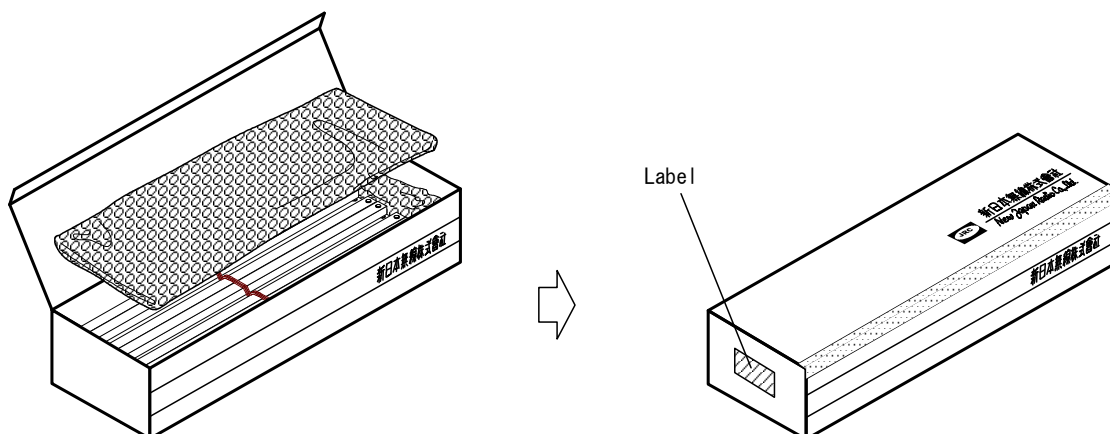
■PACKING SPEC

Unit: mm

STICK STATE



PACKING STATE

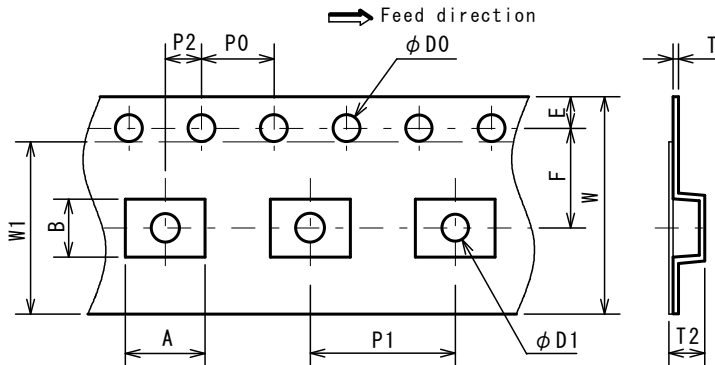


TVSP8(MSOP8) MEET JEDEC MO-187-DA/THIN TYPE

PACKING SPEC

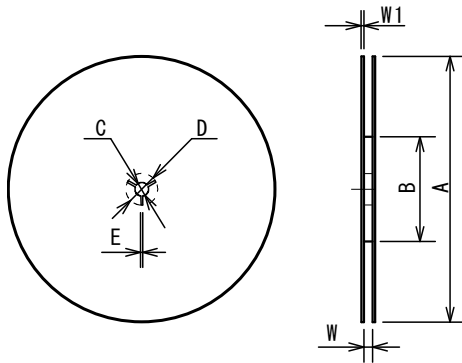
Unit: mm

TAPING DIMENSIONS



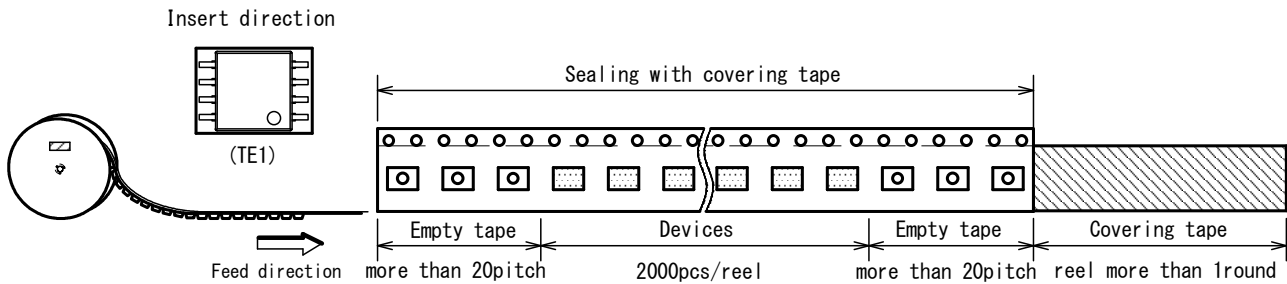
SYMBOL	DIMENSION	REMARKS
A	4.4	BOTTOM DIMENSION
B	3.2	BOTTOM DIMENSION
D0	$1.5^{+0.1}_0$	
D1	$1.5^{+0.1}_0$	
E	1.75 ± 0.1	
F	5.5 ± 0.05	
P0	4.0 ± 0.1	
P1	8.0 ± 0.1	
P2	2.0 ± 0.05	
T	0.30 ± 0.05	
T2	1.75 (MAX.)	
W	12.0 ± 0.3	
W1	9.5	THICKNESS 0.1max

REEL DIMENSIONS

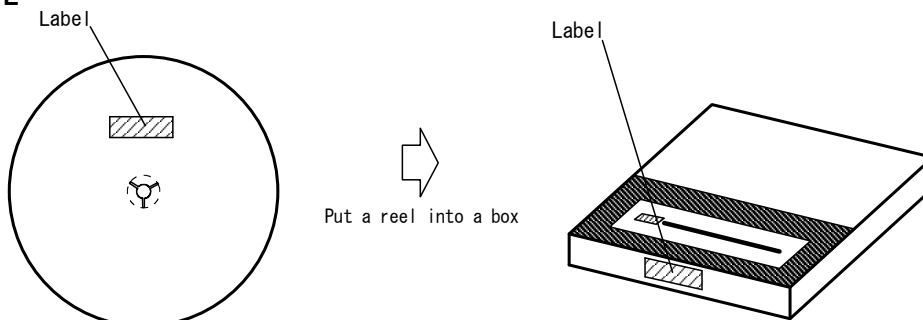


SYMBOL	DIMENSION
A	$\phi 254 \pm 2$
B	$\phi 100 \pm 1$
C	$\phi 13 \pm 0.2$
D	$\phi 21 \pm 0.8$
E	2 ± 0.5
W	13.5 ± 0.5
W1	2.0 ± 0.2

TAPING STATE

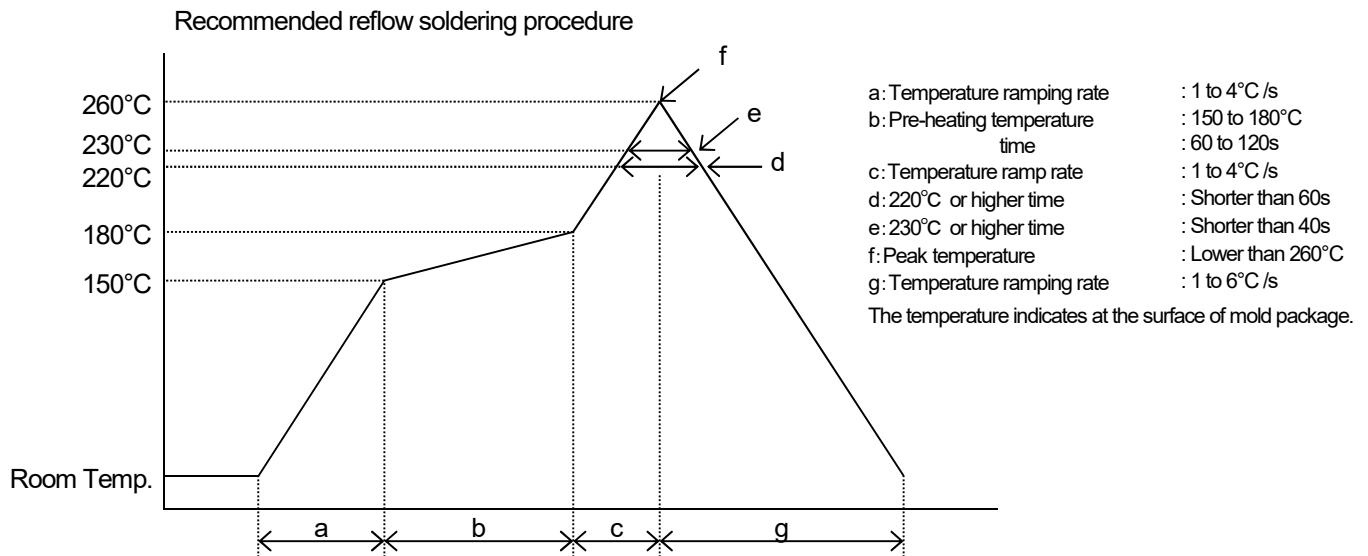


PACKING STATE

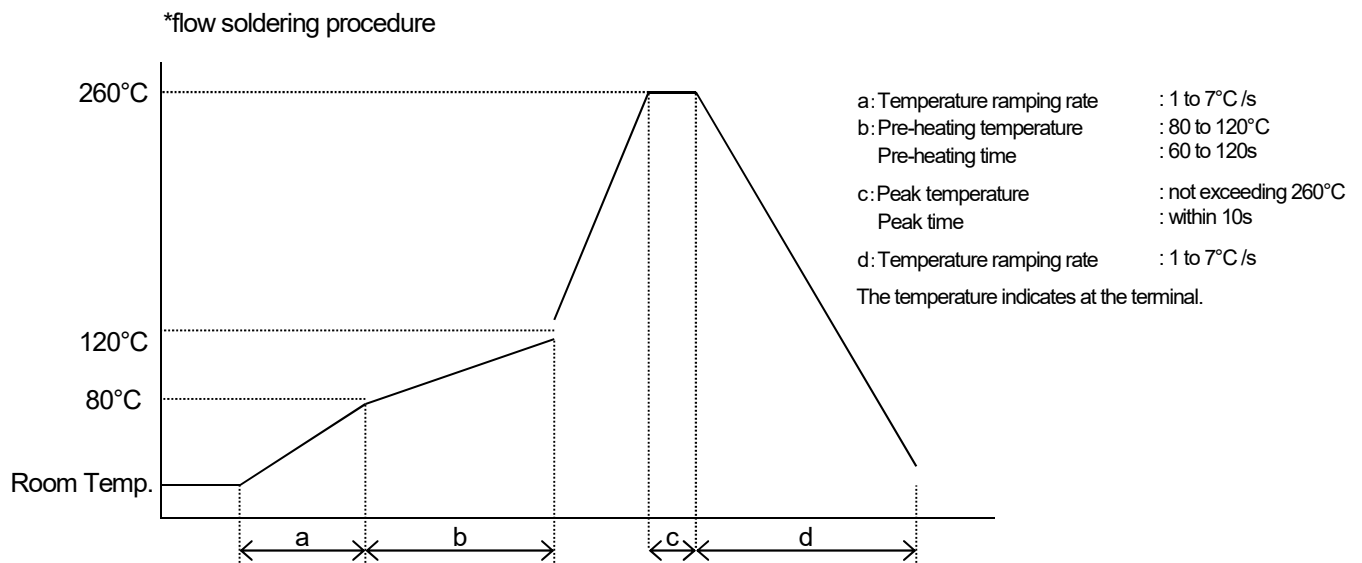


■RECOMMENDED MOUNTING METHOD

INFRARED REFLOW SOLDERING METHOD



INFRARED FLOW SOLDERING METHOD



■REVISION HISTORY

Date	Revision	Changes
11.Jun.2018.	1.0	New Release
22.Aug.2018	1.1	Add the Technical Information. (FUNCTION EXPLAMATION, OPERATION EXPLAMATION, APPLICATION EXAMPLE)
07.Feb.2019	1.2	Correction of error

[CAUTION]

1. New JRC strives to produce reliable and high quality semiconductors. New JRC's semiconductors are intended for specific applications and require proper maintenance and handling. To enhance the performance and service of New JRC's semiconductors, the devices, machinery or equipment into which they are integrated should undergo preventative maintenance and inspection at regularly scheduled intervals. Failure to properly maintain equipment and machinery incorporating these products can result in catastrophic system failures
2. The specifications on this datasheet are only given for information without any guarantee as regards either mistakes or omissions. The application circuits in this datasheet are described only to show representative usages of the product and not intended for the guarantee or permission of any right including the industrial rights.
All other trademarks mentioned herein are property of their respective companies.
3. To ensure the highest levels of reliability, New JRC products must always be properly handled.
The introduction of external contaminants (e.g. dust, oil or cosmetics) can result in failures of semiconductor products.
4. New JRC offers a variety of semiconductor products intended for particular applications. It is important that you select the proper component for your intended application. You may contact New JRC's Sale's Office if you are uncertain about the products listed in this catalog.
5. Special care is required in designing devices, machinery or equipment which demand high levels of reliability. This is particularly important when designing critical components or systems whose failure can foreseeably result in situations that could adversely affect health or safety. In designing such critical devices, equipment or machinery, careful consideration should be given to amongst other things, their safety design, fail-safe design, back-up and redundancy systems, and diffusion design.
6. The products listed in the catalog may not be appropriate for use in certain equipment where reliability is critical or where the products may be subjected to extreme conditions. You should consult our sales office before using the products in any of the following types of equipment.

Aerospace Equipment
Equipment Used in the Deep sea
Power Generator Control Equipment (Nuclear, Steam, Hydraulic)
Life Maintenance Medical Equipment
Fire Alarm/Intruder Detector
Vehicle Control Equipment (airplane, railroad, ship, etc.)
Various Safety devices

7. New JRC's products have been designed and tested to function within controlled environmental conditions. Do not use products under conditions that deviate from methods or applications specified in this catalog. Failure to employ New JRC products in the proper applications can lead to deterioration, destruction or failure of the products. New JRC shall not be responsible for any bodily injury, fires or accident, property damage or any consequential damages resulting from misuse or misapplication of its products. Products are sold without warranty of any kind, either express or implied, including but not limited to any implied warranty of merchantability or fitness for a particular purpose.
8. Warning for handling Gallium and Arsenic(GaAs) Products (Applying to GaAs MMIC, Photo Reflector). This Products uses Gallium(Ga) and Arsenic(As) which are specified as poisonous chemicals by law. For the prevention of a hazard, do not burn, destroy, or process chemically to make them as gas or power. When the product is disposed, please follow the related regulation and do not mix this with general industrial waste or household waste.
9. The product specifications and descriptions listed in this catalog are subject to change at any time, without notice.



Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[NJR:](#)

[NJU2103AD](#) [NJU2103AM](#) [NJU2103AM-TE1](#) [NJU2103ARB1-TE1](#)

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9